PRELIMINARY

3 VOLT FAST BOOT BLOCK FLASH MEMORY

28F800F3 and 28F160F3 (x16)

- **High Performance**
  - **54 MHz Effective Zero Wait-State Performance**
  - **Synchronous Burst-Mode Reads**
  - **Asynchronous Page-Mode Reads**
- **SmartVoltage Technology**
  - **2.7 V–3.6 V Read and Write Operations for Low Power Designs**
  - **12 V V_{PP} Fast Factory Programming**
- **Flexible I/O Voltage**
  - **1.65 V I/O Reduces Overall System Power Consumption**
  - **5 V-Safe I/O Enables Interfacing to 5 V Devices**
- **Enhanced Data Protection**
  - **Absolute Write Protection with V_{PP} = GND**
  - **Block Locking**
  - **Block Erase/Program Lockout during Power Transitions**
- **Density Upgrade Path**
  - **8- and 16-Mbit**
- **Manufactured on ETOX™ V Flash Technology**
- **Supports Code Plus Data Storage**
  - **Optimized for Flash Data Integrator (FDI) and other Intel® Software**
  - **Fast Program Suspend Capability**
  - **Fast Erase Suspend Capability**
- **Flexible Blocking Architecture**
  - **Eight 4-Kword Blocks for Data**
  - **32-Kword Main Blocks for Code**
  - **Top or Bottom Boot Configurations**
- **Extended Cycling Capability**
  - **Minimum 100,000 Block Erase Cycles Guaranteed**
- **Low Power Consumption**
  - **Automatic Power Savings Mode Decreases Power Consumption**
- **Automated Program and Block Erase Algorithms**
  - **Command User Interface for Automation**
  - **Status Register for System Feedback**
- **Industry-Standard Packaging**
  - **56-Lead SSOP**
  - **56-Lead TSOP**
  - **µBGA* CSP**
  - **Intel® Easy BGA(1)**

The Intel® 3 Volt Fast Boot Block Flash memory offers the highest performance synchronous burst reads—making it an ideal memory solution for burst CPUs. The Intel 3 Volt Fast Boot Block Flash memory also supports asynchronous page mode operation for non-clocked memory subsystems. Combining high read performance with the intrinsic nonvolatility of flash memory eliminates the traditional redundant memory paradigm of shadowing code from a slower nonvolatile storage source to a faster execution memory device, (e.g., SRAM SDRAM), for improved system performance. By adding 3 Volt Fast Boot Block Flash memory to your system you could reduce the total memory requirement, which helps increase reliability and reduce overall system power consumption—all while reducing system cost.

This family of products is manufactured on Intel® 0.4 µm ETOX™ V process technology. They are available in a wide variety of industry standard packaging technologies.

NOTE: This document formerly known as *Fast Boot Block Flash Memory Family 8 and 16 Mbit*.

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(1) New Packages in 1999:

Please see http://developer.intel.com/design/flash/packdata/index.com for the latest information on the new easy-to-use BGA packages.

March 1999

Order Number: 290644-003

CONTENTS

REVISION HISTORY

Date of Revision	Version	Description
05/12/98	-001	Original version
11/15/98	-002	Minor text modifications Revised Page mode read waveform Revised Single synchronous read waveform Improved automotive specifications Changed name from *Fast Boot Block Flash Memory Family 8 and 16 Mbit.*
03/22/99	-003	Added Easy BGA pinout graphic Added TSOP and Easy BGA part number nomenclature

1.0 INTRODUCTION

This datasheet contains 8- and 16-Mbit 3 Volt Fast Boot Block Flash memory information. Section 1.0 provides a flash memory overview. Sections 2.0 through 8.0 describe the memory functionality and electrical specifications for extended and automotive temperature product offerings.

1.2 Product Overview

The 3 Volt Fast Boot Block Flash memory provides density upgrades with pinout compatibility for 8- and 16-Mbit densities. This family of products are high performance, low voltage memories with a 16-bit data bus and individually erasable blocks. These blocks are optimally sized for code and data storage. Eight 4-Kword parameter blocks are positioned at either the top (denoted by -T suffix) or bottom (denoted by -B suffix) of the address map. The rest of the device is grouped into 32-Kword main blocks. The upper two (or lower two) parameter blocks can be locked (WP# = V_{IL}) for complete code protection. (Automotive block locking scheme is two parameter blocks and all main blocks when WP# = V_{IL}.)

The device's optimized architecture and interface dramatically increases read performance beyond previously attainable levels. It supports synchronous burst reads and asynchronous page-mode reads from main blocks (parameter blocks support single synchronous and asynchronous reads). Upon initial power-up or return from reset, the main blocks of the device default to a page-mode read configuration. Page-mode read configuration is ideal for non-clocked memory systems and is compatible with page-mode ROM. Synchronous burst reads are enabled by configuring the Read Configuration Register using the standard two bus cycle algorithm. In synchronous burst mode, the CLK input increments an internal burst address generator, synchronizes the flash memory with the host CPU, and outputs data on every rising (or falling) CLK edge up to 54 MHz (40 MHz for automotive temperature). An output signal, WAIT#, is also provided to ease CPU to flash memory communication and synchronization during continuous burst operations that are not initiated on a 4-word boundary.

In addition to the enhanced architecture and optimized interface, this family of products incorporates SmartVoltage technology which enables fast 12 Volt factory programming and 2.7 V–3.6 V in system programming for low power designs. Specifically designed for low voltage systems, 3 Volt Fast Boot Block Flash memory components support read operations at 2.7 V–3.6 V (3.0 V–3.6 V for automotive temperature) V_{CC} and block erase and program operations at 2.7 V–3.6 V (3.0 V–3.6 V for automotive temperature) and 12 V V_{PP}. The 12 V V_{PP} option renders the fastest program performance to increase factory programming throughput. With the 2.7 V –3.6 V (3.0 V–3.6 V for automotive temperature) V_{PP} option, V_{CC} and V_{PP} can be tied together for a simple, low power design. In addition to the voltage flexibility, the dedicated V_{PP} pin gives complete data protection when $V_{PP} \leq V_{PPLK}$.

The flexible input/output (I/O) voltage feature of the device helps reduce system power consumption and simplifies interfacing to sub 2.7 V CPUs. Powered by the V_{CCQ} pins, the I/O buffers can operate independently of the core voltage. The Flexible I/O ring of the device works in three modes:

1. With V_{CCQ} voltage at 1.65 V, the I/Os can swing between GND and 1.65 V, reducing I/O power consumption by 65% over standard 3 V flash memory components.
2. With V_{CC} and V_{CCQ} at 2.7 V–3.6V the device is an ideal fit for single supply voltage, low power, and battery powered applications.
3. The 5 V-safe feature allows easy interface to 5 V I/O systems by tolerating 5 V CMOS input levels. This helps ease CPU interfacing by adapting to CPU's bus voltage without using buffers or level shifters.

The device's Command User Interface (CUI) serves as the interface between the system processor and internal flash memory operation. A valid command sequence written to the CUI initiates device automation. This automation is controlled by an internal Write State Machine (WSM) which automatically executes the algorithms and timings necessary for block erase and program operations. The status register provides WSM feedback by signifying block erase or program completion and status.

Block erase and program automation allows erase and program operations to be executed using an industry-standard two-write command sequence. A block erase operation erases one block at a time, and data is programmed in word (16 bit) increments. The erase suspend feature allows

system software to suspend an ongoing block erase operation in order to read from or program data to any other block. The program suspend feature allows system software to suspend an ongoing program operation in order to read from any other location.

The 3 Volt Fast Boot Block Flash memory devices offer two low power savings features: Automatic Power Savings (APS) and standby mode. The device automatically enters APS mode following the completion of a read cycle. Standby mode is initiated when the system deselects the device by driving CE# inactive or RST# active. RST# also resets the device to read array, provides write protection, and clears the status register. Combined, these two features significantly reduce power consumption.

2.0 PRODUCT DESCRIPTION

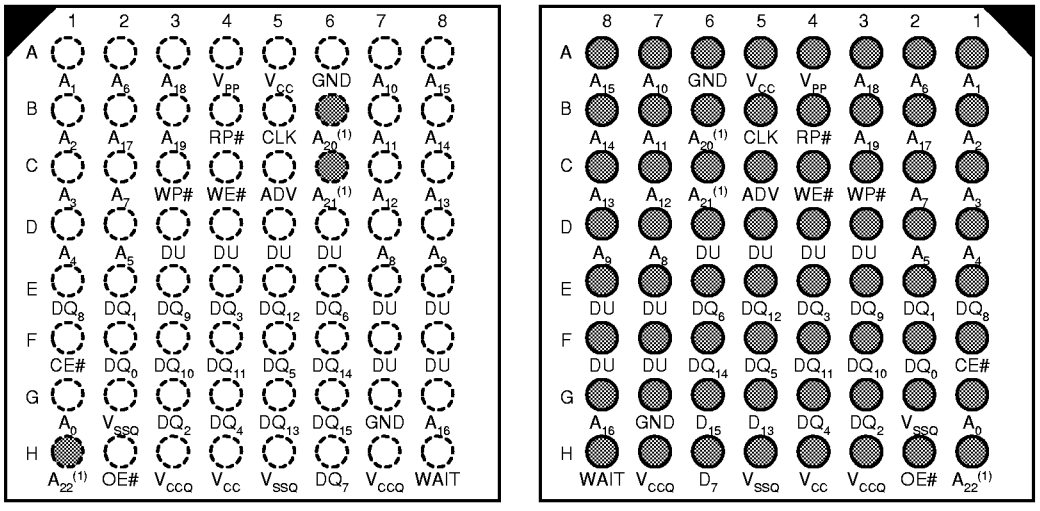
This section describes the pinout and block architecture of the device family.

2.1 Pinouts

The Intel 3 Volt Fast Boot Block Flash memory provides upgrade paths in each package pinout up to the 16-Mbit density. The family is available in Easy BGA, µBGA CSP, 56-lead SSOP and 56-lead TSOP packages. Pinouts for the 8- and 16-Mbit components are illustrated in Figures 1, 2, 3 and 4.

2.2 Pin Description

The pin description table describes pin usage.



Top View - Ball Side Down

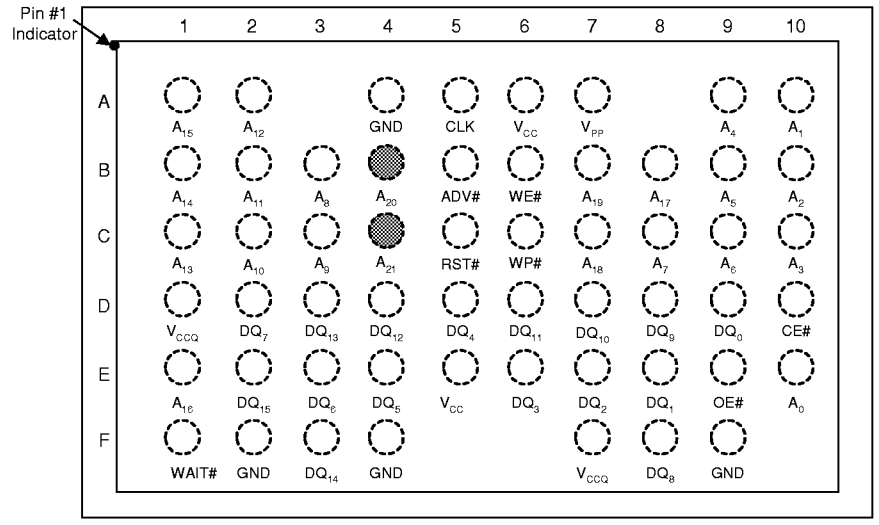
Bottom View - Ball Side Up

EasyPin01

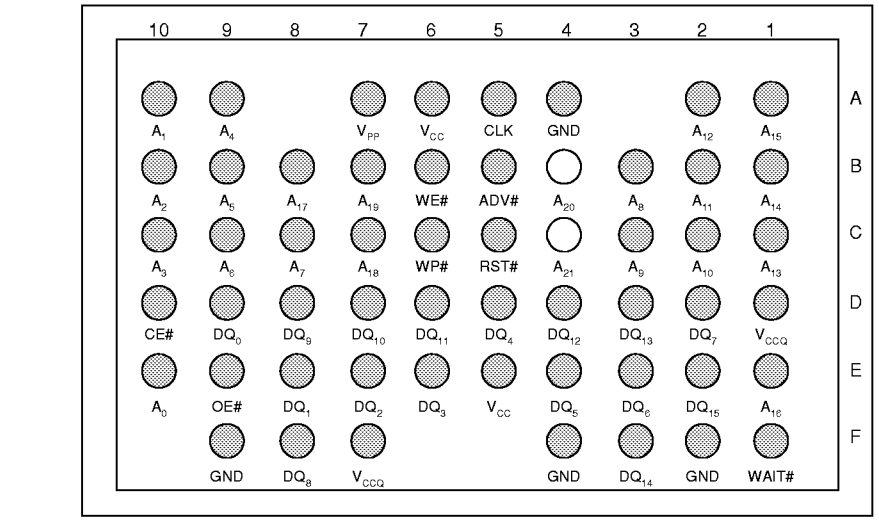
NOTES:

1. A_{20} is only valid on 32-Mbit densities and above, A_{21} is only valid on 64-Mbit densities and above, A_{22} is only valid on 128-Mbit densities and above (currently not on roadmap). All locations are populated with solder balls
2. Shaded connections on the Top View indicate possible future upgrade address connections.
3. Reference the *Preliminary Mechanical Specification for Easy BGA Package* at the Intel® Flash Packaging Data website, http://developer.intel.com/design/flash/packdata/index.htm, for detailed package specifications.

Figure 1. 8 x 8 Easy BGA Package Ballout



Top View, Ball Side Down

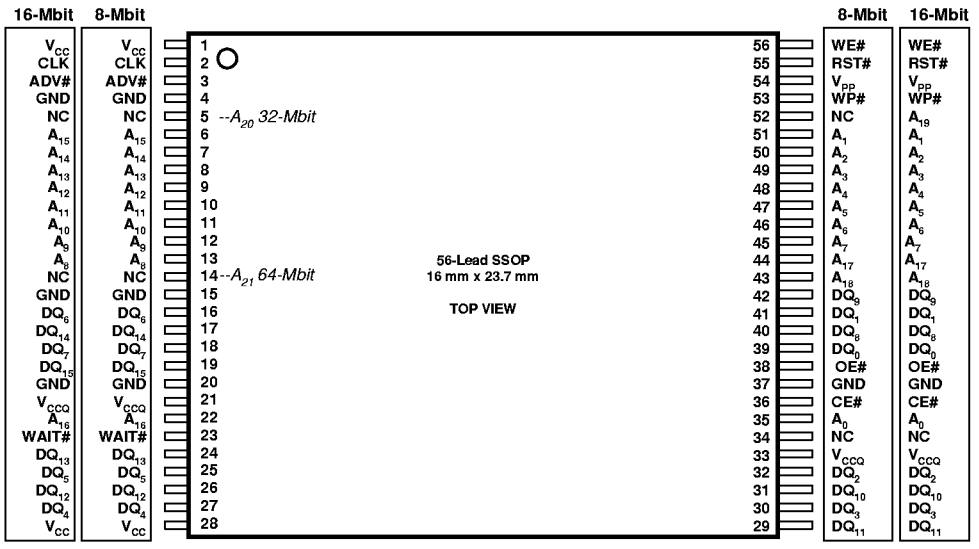


Bottom View, Ball Side Up

NOTES:

1. Shaded connections on the Top View indicate upgrade address connections. Lower density deviceswill not have upper address solder balls. Routing is not recommended in this area.
2. A_{20} and A_{21} are the upgrade addresses for potential 32-Mbit and 64-Mbit devices (currently not on road map).
3. Reference the *µBGA* Package Mechanical and Shipping Media Specification* at the Intel® Flash Packaging Data website, http://developer.intel.com/design/flash/packdata/index.htm, for detailed package specifications.

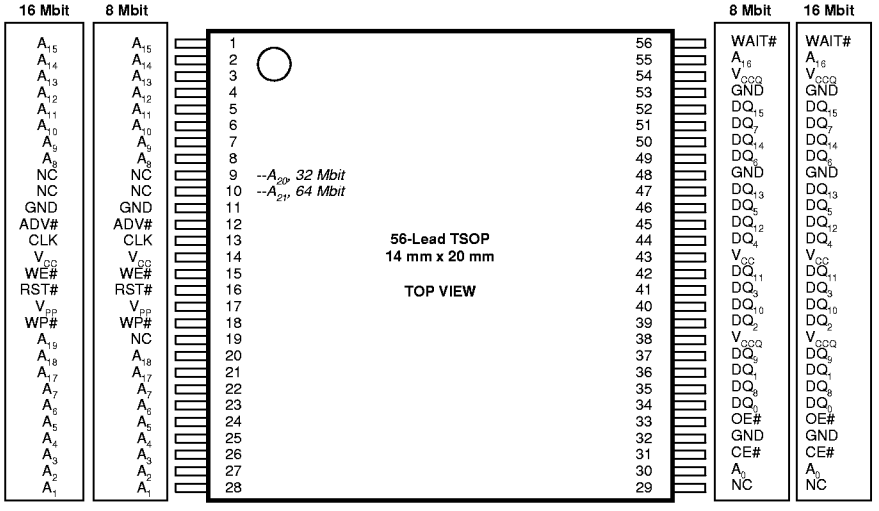
Figure 2. 56-Ball µBGA* Package Ballout



NOTE:

A_{20} and A_{21} are the upgrade addresses for potential 32-Mbit and 64-Mbit devices (currently not on road map).

Figure 3. SSOP Pinout



NOTE:

A_{20} and A_{21} are the upgrade addresses for potential 32-Mbit and 64-Mbit devices (currently not on road map).

Figure 4. TSOP Pinout

Table 1. Pin Descriptions

Sym	Type	Name and Function
A_0–A_{19}	INPUT	**ADDRESS INPUTS:** Inputs for addresses during read and write operations. Addresses are internally latched during read and write cycles. 8-Mbit: $A_{0–18}$, 16-Mbit: $A_{0–19}$
DQ_0–DQ_{15}	INPUT/ OUTPUT	**DATA INPUT/OUTPUTS:** Inputs data and commands during write cycles, outputs data during memory array, status register (DQ_0–DQ_7), and identifier code read cycles. Data pins float to high-impedance when the chip is deselected or outputs are disabled. Data is internally latched during a write cycle.
CLK	INPUT	**CLOCK:** Synchronizes the flash memory to the system operating frequency during synchronous burst-mode read operations. When configured for synchronous burst-mode reads, the address is latched on the first rising (or falling, depending upon the read configuration register setting) CLK edge when ADV# is active or upon a rising ADV# edge, whichever occurs first. CLK is ignored during asynchronous page-mode read and write operations.
ADV#	INPUT	**ADDRESS VALID:** Indicates that a valid address is present on the address inputs. Addresses are latched on the rising edge of ADV# during read and write operations. ADV# may be tied active during asynchronous read and write operations.
CE#	INPUT	**CHIP ENABLE:** Activates the device's control logic, input buffers, decoders, and sense amplifiers. CE#-high deselects the device and reduces power consumption to standby levels.
RST#	INPUT	**RESET:** When driven low, RST# inhibits write operations which provides data protection during power transitions, and it resets internal automation. RST#-high enables normal operation. Exit from reset sets the device to asynchronous read array mode.
OE#	INPUT	**OUTPUT ENABLE:** Gates data outputs during a read cycle.
WE#	INPUT	**WRITE ENABLE:** Controls writes to the CUI and array. Addresses and data are latched on the rising edge of the WE# pulse.
WP#	INPUT	**WRITE PROTECTION:** Provides a method for locking and unlocking all main blocks and two parameter blocks. When WP# is at logic low, lockable blocks are locked. If a program or erase operation is attempted on a locked block, SR.1 and either SR.4 [program] or SR.5 [block erase] will be set to indicate the operation failed. When WP# is at logic high, the lockable blocks are unlocked and can be programmed or erased.
WAIT#	OUTPUT	**WAIT:** Provides data valid feedback only when configured for synchronous burst-mode and the burst length is set to continuous. This signal is gated by OE# and CE# and is internally pull-up to V_{CCQ} via a resistor. WAIT# from several components can be tied together to form one system WAIT# signal.

Table 1. Pin Descriptions (Continued)

Sym	Type	Name and Function
V_{PP}	SUPPLY	**BLOCK ERASE AND PROGRAM POWER SUPPLY (2.7 V–3.6 V, 11.4 V–12.6 V):** For erasing array blocks or programming data, a valid voltage must be applied to this pin. With $V_{PP} \leq V_{PPLK}$, memory contents cannot be altered. Block erase and program with an invalid V_{PP} voltage should not be attempted. Applying 11.4 V–12.6 V to V_{PP} can only be done for a maximum of 1000 cycles on main blocks and 2500 cycles on the parameter blocks. V_{PP} may be connected to 12 V for a total of 80 hours maximum (see Section 6.0 for details).
V_{CC}	SUPPLY	**DEVICE POWER SUPPLY (2.7 V–3.6 V):** With $V_{CC} \leq V_{LKO}$, all write attempts to the flash memory are inhibited. Device operations at invalid V_{CC} voltages should not be attempted.
V_{CCQ}	SUPPLY	**OUTPUT POWER SUPPLY (1.65 V–2.5 V, 2.7 V–3.6 V):** Enables all outputs to be driven to 1.65 V to 2.5 V or 2.7 V to 3.6 V. When V_{CCQ} equals 1.65 V–2.5 V, V_{CC} voltage must not exceed 3.3 V and should be regulated to 2.7 V–2.85 V to achieve lowest power operation (see *DC Characteristics* for detailed information). For 5 V-tolerant operation V_{CCQ} must equal V_{CC} voltage and must be regulated to 2.7 V to 3.6 V. This input may be tied directly to V_{CC}.
GND	SUPPLY	**GROUND:** Do not float any ground pins.
NC		**NO CONNECT:** Lead is not internally connected; it may be driven or floated. (Pins noted as possible upgrades to 32-Mbit and 64-Mbit densities can be connected to the appropriate address lines to pre-enable designs for possible future devices. Currently there is not a 32- or 64-Mbit on the roadmap).

2.3 Memory Blocking Organization

The 3 Volt Fast Boot Block Flash memory family is an asymmetrically-blocked architecture that enables system integration of code and data within a single flash device. For the address locations of each block, see the memory maps in Figure 5 (top boot blocking) and Figure 6 (bottom boot blocking).

2.3.1 PARAMETER BLOCKS

The 3 Volt Fast Boot Block Flash memory architecture includes parameter blocks to facilitate storage of frequently updated small parameters that would normally be stored in an EEPROM. By using software techniques, the word-rewrite functionality of EEPROMs can be emulated. Each 8- and 16-Mbit device contains eight 4-Kwords (4,096-words) parameter blocks.

2.3.2 MAIN BLOCKS

After the parameter blocks, the remainder of the array is divided into equal size main blocks for code and/or data storage. The Main blocks are the area of the device that support 4, 8, and Continuous Burst operations. The 8-Mbit device contains fifteen 32-Kword (32,768-word) main blocks, and the 16-Mbit device contains thirty-one 32-Kword (32,768-word) main blocks.

	8-Mbit	Address Range
Block 22	4-KWord	7F000h - 7FFFFh
Block 21	4-KWord	7E000h - 7EFFFh
Block 20	4-KWord	7D000h - 7DFFFh
Block 19	4-KWord	7C000h - 7CFFFh
Block 18	4-KWord	7B000h - 7BFFFh
Block 17	4-KWord	7A000h - 7AFFFh
Block 16	4-KWord	79000h - 79FFFh
Block 15	4-KWord	78000h - 78FFFh
Block 14	32-KWord	70000h - 77FFFh
Block 13	32-KWord	68000h - 6FFFFh
Block 12	32-KWord	60000h - 67FFFh
Block 11	32-KWord	58000h - 5FFFFh
Block 10	32-KWord	50000h - 57FFFh
Block 9	32-KWord	48000h - 4FFFFh
Block 8	32-KWord	40000h - 47FFFh
Block 7	32-KWord	38000h - 3FFFFh
Block 6	32-KWord	30000h - 37FFFh
Block 5	32-KWord	28000h - 2FFFFh
Block 4	32-KWord	20000h - 27FFFh
Block 3	32-KWord	18000h - 1FFFFh
Block 2	32-KWord	10000h - 17FFFh
Block 1	32-KWord	08000h - 0FFFFh
Block 0	32-KWord	00000h - 07FFFh

	16-Mbit	Address Range
Block 38	4-KWord	FF000h - FFFFFh
Block 37	4-KWord	FE000h - FEFFFh
Block 36	4-KWord	FD000h - FDFFFh
Block 35	4-KWord	FC000h - FCFFFh
Block 34	4-KWord	FB000h - FBFFFh
Block 33	4-KWord	FA000h - FAFFFh
Block 32	4-KWord	F9000h - F9FFFh
Block 31	4-KWord	F8000h - F8FFFh
Block 30	32-KWord	F0000h - F7FFFh
Block 29	32-KWord	E8000h - EFFFFh
Block 28	32-KWord	E0000h - E7FFFh
Block 27	32-KWord	D8000h - DFFFFh
Block 26	32-KWord	D0000h - D7FFFh
Block 25	32-KWord	C8000h - CFFFFh
Block 24	32-KWord	C0000h - C7FFFh
Block 23	32-KWord	B8000h - BFFFFh
Block 22	32-KWord	B0000h - B7FFFh
Block 21	32-KWord	A8000h - AFFFFh
Block 20	32-KWord	A0000h - A7FFFh
Block 19	32-KWord	98000h - 9FFFFh
Block 18	32-KWord	90000h - 97FFFh
Block 17	32-KWord	88000h - 8FFFFh
Block 16	32-KWord	80000h - 87FFFh
Block 15	32-KWord	78000h - 7FFFFh
Block 14	32-KWord	70000h - 77FFFh
Block 13	32-KWord	68000h - 6FFFFh
Block 12	32-KWord	60000h - 67FFFh
Block 11	32-KWord	58000h - 5FFFFh
Block 10	32-KWord	50000h - 57FFFh
Block 9	32-KWord	48000h - 4FFFFh
Block 8	32-KWord	40000h - 47FFFh
Block 7	32-KWord	38000h - 3FFFFh
Block 6	32-KWord	30000h - 37FFFh
Block 5	32-KWord	28000h - 2FFFFh
Block 4	32-KWord	20000h - 27FFFh
Block 3	32-KWord	18000h - 1FFFFh
Block 2	32-KWord	10000h - 17FFFh
Block 1	32-KWord	08000h - 0FFFFh
Block 0	32-KWord	00000h - 07FFFh

Figure 5. 8- and 16-Mbit Top Boot Memory Map

	8-Mbit	Address Range
Block 22	32-KWord	78000h - 7FFFFh
Block 21	32-KWord	70000h - 77FFFh
Block 20	32-KWord	68000h - 6FFFFh
Block 19	32-KWord	60000h - 67FFFh
Block 18	32-KWord	58000h - 5FFFFh
Block 17	32-KWord	50000h - 57FFFh
Block 16	32-KWord	48000h - 4FFFFh
Block 15	32-KWord	40000h - 47FFFh
Block 14	32-KWord	38000h - 3FFFFh
Block 13	32-KWord	30000h - 37FFFh
Block 12	32-KWord	28000h - 2FFFFh
Block 11	32-KWord	20000h - 27FFFh
Block 10	32-KWord	18000h - 1FFFFh
Block 9	32-KWord	10000h - 17FFFh
Block 8	32-KWord	08000h - 0FFFFh
Block 7	4-KWord	07000h - 07FFFh
Block 6	4-KWord	06000h - 06FFFh
Block 5	4-KWord	05000h - 05FFFh
Block 4	4-KWord	04000h - 04FFFh
Block 3	4-KWord	03000h - 03FFFh
Block 2	4-KWord	02000h - 02FFFh
Block 1	4-KWord	01000h - 01FFFh
Block 0	4-KWord	00000h - 00FFFh

	16-Mbit	Address Range
Block 38	32-KWord	F8000h - FFFFFh
Block 37	32-KWord	F0000h - F7FFFh
Block 36	32-KWord	E8000h - EFFFFh
Block 35	32-KWord	E0000h - E7FFFh
Block 34	32-KWord	D8000h - DFFFFh
Block 33	32-KWord	D0000h - D7FFFh
Block 32	32-KWord	C8000h - CFFFFh
Block 31	32-KWord	C0000h - C7FFFh
Block 30	32-KWord	B8000h - BFFFFh
Block 29	32-KWord	B0000h - B7FFFh
Block 28	32-KWord	A8000h - AFFFFh
Block 27	32-KWord	A0000h - A7FFFh
Block 26	32-KWord	98000h - 9FFFFh
Block 25	32-KWord	90000h - 97FFFh
Block 24	32-KWord	88000h - 8FFFFh
Block 23	32-KWord	80000h - 87FFFh
Block 22	32-KWord	78000h - 7FFFFh
Block 21	32-KWord	70000h - 77FFFh
Block 20	32-KWord	68000h - 6FFFFh
Block 19	32-KWord	60000h - 67FFFh
Block 18	32-KWord	58000h - 5FFFFh
Block 17	32-KWord	50000h - 57FFFh
Block 16	32-KWord	48000h - 4FFFFh
Block 15	32-KWord	40000h - 47FFFh
Block 14	32-KWord	38000h - 3FFFFh
Block 13	32-KWord	30000h - 37FFFh
Block 12	32-KWord	28000h - 2FFFFh
Block 11	32-KWord	20000h - 27FFFh
Block 10	32-KWord	18000h - 1FFFFh
Block 9	32-KWord	10000h - 17FFFh
Block 8	32-KWord	08000h - 0FFFFh
Block 7	4-KWord	07000h - 07FFFh
Block 6	4-KWord	06000h - 06FFFh
Block 5	4-KWord	05000h - 05FFFh
Block 4	4-KWord	04000h - 04FFFh
Block 3	4-KWord	03000h - 03FFFh
Block 2	4-KWord	02000h - 02FFFh
Block 1	4-KWord	01000h - 01FFFh
Block 0	4-KWord	00000h - 00FFFh

Figure 6. 8- and 16-Mbit Bottom Boot Memory Map

3.0 PRINCIPLES OF OPERATION

The 3 Volt Fast Boot Block Flash memory components include an on-chip Write State Machine (WSM) to manage block erase and program. It allows for CMOS-level control inputs, fixed power supplies, and minimal processor overhead with RAM-like interface timings.

3.1 Bus Operations

All bus cycles to and from flash memory conform to standard microprocessor bus cycles.

3.1.1 READ

The flash memory has three read modes available: read array, identifier codes, and status register. These modes are accessible independent of the V_{PP} voltage. The appropriate read command (Read Array, Read Identifier Codes, or Read Status Register) must be written to the CUI to enter the requested read mode. Upon initial power-up or exit from reset, the device defaults to read array mode.

When reading information from main blocks in read array mode, the device supports two high-performance read configurations: synchronous burst-mode and asynchronous page-mode. Synchronous burst-mode, is enabled by writing to the read configuration register. This register sets the read configuration, burst order, frequency configuration, and burst length. In synchronous burst-mode, the device latches the initial address then outputs a sequence of data with respect to the input CLK and read configuration setting. Asynchronous page-mode is the default state and provides high data transfer rate for non-clocked memory subsystems. In this state, data is internally read and stored in a high-speed page buffer. $A_{1:0}$ addresses data in the page buffer. The page size is four words.

Read operations from the parameter blocks, identifier codes and status register transpire as single synchronous or asynchronous read cycles. The read configuration register setting determines whether or not read operations are synchronous or asynchronous.

For all read operations, CE# must be driven active to enable the devices, ADV# must be driven low to open the internal address latch, and OE# must be driven low to activate the outputs. In asynchronous mode, the address is latched when ADV# is driven high. In synchronous mode, the address is latched by ADV# going high or ADV# low in conjunction with a rising (falling) clock edge, whichever occurs first. WE# must be at V_{IH}. Figures 15 through 20 illustrate the different read cycles.

3.1.2 OUTPUT DISABLE

With OE# at a logic-high level (V_{IH}), the device outputs are disabled. Output pins DQ_0–DQ_{15} are placed in a high-impedance state.

3.1.3 STANDBY

Deselecting the device by bringing CE# to a logic-high level (V_{IH}) places the device in standby mode, which substantially reduces device power consumption. In standby, outputs are placed in a high-impedance state independent of OE#. If deselected during program or erase operation, the device continues to consume active power until the program or erase operation is complete.

3.1.4 WRITE

Commands are written to the CUI using standard microprocessor write timings when ADV#, WE#, and CE# are active and OE# inactive. The CUI does not occupy an addressable memory location. The address is latched on the rising edge of ADV#, WE#, or CE# (whichever occurs first) and data needed to execute a command is latched on the rising edge of WE# or CE# (whichever goes high first). Write operations are asynchronous. Therefore, CLK is ignored during write operations. Figure 22 illustrates a write operation.

3.1.5 RESET

The device enters a reset mode when RST# is driven low. In reset mode, internal circuitry is turned off and outputs are placed in a high-impedance state.

After return from reset, a time t_{PHQV} is required until outputs are valid, and a delay (t_{PHWL} or t_{PHEL}) is required before a write sequence can be initiated. After this wake-up interval, normal operation is restored. The device defaults to read array mode, the status register is set to 80H, and the read configuration register defaults to asynchronous page-mode reads.

If RST# is taken low during a block erase or program operation, the operation will be aborted and the memory contents at the aborted location are no longer valid. See Figure 23 for detailed information regarding reset timings.

4.0 COMMAND DEFINITIONS

Device operations are selected by writing specific commands into the CUI. Table 3 defines these commands.

Table 2. Bus Operations

Mode	Notes	RST#	CE#	ADV#	OE#	WE#	Address	V_{PP}	DQ_{0-15}
Reset		V_{IL}	X	X	X	X	X	X	High Z
Standby		V_{IH}	V_{IH}	X	X	X	X	X	High Z
Output Disable		V_{IH}	V_{IL}	X	V_{IH}	V_{IH}	X	X	High Z
Read	1,2	V_{IH}	V_{IL}	V_{IL}	V_{IL}	V_{IH}	X	X	D_{OUT}
Read Identifier Codes		V_{IH}	V_{IL}	V_{IL}	V_{IL}	V_{IH}	See Table 4	X	See Table 4
Write	3,4	V_{IH}	V_{IL}	V_{IL}	V_{IH}	V_{IL}	X	X	D_{IN}

NOTES:

1. Refer to *DC Characteristics*. When $V_{PP} \le V_{PPLK}$, memory contents can be read, but not altered.
2. X can be V_{IL} or V_{IH} for control and address input pins and V_{PPLK} or $V_{PPH1/2}$ for V_{PP}. See *DC Characteristics* for V_{PPLK} and $V_{PPH1/2}$ voltages.
3. Command writes involving block erase or program are reliably executed when $V_{PP} = V_{PPH1/2}$ and $V_{CC} = V_{CC1/2}$ (see Section 8 for operating conditions at different temperatures).
4. Refer to Table 3 for valid D_{IN} during a write operation.

Table 3. Command Definitions(1)

Command	Bus Cycles Req'd.	Notes	First Bus Cycle			Second Bus Cycle		
			Oper(2)	Addr(3)	Data(4)	Oper(2)	Addr(3)	Data(4)
Read Array/Reset	1		Write	X	FFH			
Read Identifier Codes	≥ 2	5	Write	X	90H	Read	IA	ID
Read Status Register	2		Write	X	70H	Read	X	SRD
Clear Status Register	1		Write	X	50H			
Block Erase	2	6,7	Write	X	20H	Write	BA	D0H
Program	2	6,7,8	Write	X	40H or 10H	Write	WA	WD
Block Erase and Program Suspend	1	6	Write	X	B0H			
Block Erase and Program Resume	1	6	Write	X	D0H			
Set Read Configuration	2		Write	RCD	60H	Write	RCD	03H

NOTES:

1. Commands other than those shown above are reserved by Intel for future device implementations and should not be used.
2. Bus operations are defined in Table 2.
3. X = Any valid address within the device.
   IA = Identifier Code Address.
   BA = Address within the block being erased.
   WA = Address of memory location to be written.
   RCD = Data to be written to the read configuration register. This data is presented to the device on A_{15-0}; set all other address inputs to "0."
4. SRD = Data read from status register. See Table 5 for a description of the status register bits.
   WD = Data to be written at location WA. Data is latched on the rising edge of WE# or CE# (whichever goes high first).
   ID = Data read from identifier codes. See Table 4 for manufacturer and device codes.
   RCD = Data to be written to read configuration register. See Table 6 for a description of the read configuration register bits.
5. Following the Read Identifier Codes command, read operations access manufacturer, device codes, and read configuration register.
6. Following a block erase, program, and suspend operation, read operations access the status register.
7. To issue a block erase, program, or suspend operation to a lockable block, hold WP# at V_{IH}.
8. Either 40H or 10H are recognized by the WSM as the program setup.

4.1 Read Array Command

Upon initial device power-up or exit from reset, the device defaults to read array mode. The read configuration register defaults to asynchronous page-mode. The Read Array command also causes the device to enter read array mode. The device remains enabled for reads until another command is written. Once the internal WSM has started a block erase or program, the device will not recognize the Read Array command until the WSM completes its operation or unless the WSM is suspended via an Erase or Program Suspend command. The Read Array command functions independently of the V_{PP} voltage.

4.2 Read Identifier Codes Command

The identifier code operation is initiated by writing the Read Identifier Codes command. After writing the command, read cycles retrieve the manufacturer and device codes (see Table 4 for identifier code values). Page-mode and burst reads are not supported in this read mode. To terminate the operation, write another valid command, like the Read Array command. The Read Identifier Codes command functions independently of the V_{PP} voltage.

Table 4. Identifier Codes

Code			Address (Hex)	Data (Hex)
Manufacturer Code			00000	0089
Device Code	8 Mbit	-T	00001	88F1
		-B	00001	88F2
	16 Mbit	-T	00001	88F3
		-B	00001	88F4

4.3 Read Status Register Command

The status register can be read at any time by writing the Read Status Register command to the CUI. After writing this command, all subsequent read operations output status register data until another valid command is written. Page-mode and burst reads are not supported in this read mode. The status register content is updated and latched on the rising edge of ADV# or rising (falling) CLK edge when ADV# is low during synchronous burst-mode or the falling edge of OE# or CE#, whichever occurs first. The Read Status Register command functions independently of the V_{PP} voltage.

4.4 Clear Status Register Command

Status register bits SR.5, SR.4, SR.3, and SR.1 are set to "1"s by the WSM and can only be cleared by issuing the Clear Status Register command. These bits indicate various error conditions. By allowing system software to reset these bits, several operations may be performed (such as cumulatively erasing or writing several bytes in sequence). The status register may be polled to determine if a problem occurred during the sequence. The Clear Status Register command functions independently of the applied V_{PP} voltage. After executing this command, the device returns to read array mode.

4.5 Block Erase Command

Erase is executed one block at a time and initiated by a two-cycle command. A block erase setup is written first, followed by a block erase confirm. This command sequence requires appropriate sequencing and address within the block to be erased (erase changes all block data to FFH). Block preconditioning, erase, and verify are handled internally by the WSM. After the two-cycle block erase sequence is written, the device automatically outputs status register data when read (see Figure 9, *Automated Block Erase Flowchart*). The CPU can detect block erase completion by analyzing status register bit SR.7.

When the block erase completes, check status register bit SR.5 for an error flag ("1"). If an error is detected, check status register bits SR.4, SR.3, and SR.1 to understand what caused the failure. After examining the status register, it should be cleared if an error was detected before issuing a new command. The device will remain in status register read mode until another command is written to the CUI.

Table 5. Status Register Definition

WSMS	ESS	ES	PS	VPPS	PSS	DPS	R
7	6	5	4	3	2	1	0

	NOTES:
SR.7 = WRITE STATE MACHINE STATUS (WSMS) 1 = Ready 0 = Busy	Check SR.7 to determine block erase or program completion. SR.6–0 are invalid while SR.7 = "0."
SR.6 = ERASE SUSPEND STATUS (ESS) 1 = Block Erase Suspended 0 = Block Erase in Progress/Completed	When an Erase Suspend command is issued, the WSM halts execution and sets both SR.7 and SR.6 to "1." SR.6 remains set until an Erase Resume command is written to the CUI.
SR.5 = ERASE STATUS (ES) 1 = Error in Block Erasure 0 = Successful Block Erase	If both SR.5 and SR.4 are "1"s after a block erase or program attempt, an improper command sequence was entered.
SR.4 = PROGRAM STATUS (PS) 1 = Error in Program 0 = Successful Program	
SR.3 = V_{PP} STATUS (VPPS) 1 = V_{PP} Low Detect, Operation Abort 0 = V_{PP} OK	SR.3 does not provide a continuous V_{PP} feedback. The WSM interrogates and indicates the V_{PP} level only after a block erase or program operation. SR.3 is not guaranteed to reports accurate feedback when $V_{PP} \neq V_{PPH1/2}$ or V_{PPLK}.
SR.2 = PROGRAM SUSPEND STATUS (PSS) 1 = Program Suspended 0 = Program in Progress/Completed	When an Program Suspend command is issued, the WSM halts execution and sets both SR.7 and SR.2 to "1." SR.2 remains set until an Program Resume command is written to the CUI.
SR.1 = DEVICE PROTECT STATUS (DPS) 1 = Block Erase or Program Attempted on a Locked Block, Operation Abort 0 = Unlocked	If a block erase or program operation is attempted to a locked block, SR.1 is set by the WSM and aborts the operation if WP# = V_{IL}.
SR.0 = RESERVED FOR FUTURE ENHANCEMENTS (R)	SR.0 is reserved for future use and should be masked out when polling the status register.

4.6 Program Command

Program operation is executed by a two-cycle command sequence. Program setup (standard 40H or alternate 10H) is written, followed by a second write that specifies the address and data. The WSM then takes over, controlling the internal program algorithm. After the program sequence is written, the device automatically outputs status register data when read (see Figure 10, *Automated Program Flowchart*). The CPU can detect the completion of the program event by analyzing status register bit SR.7.

When the program operation completes, check status register bit SR.4 for an error flag ("1"). If an error is detected, check status register bits SR.5, SR.3, and SR.1 to understand what caused the problem. After examining the status register, it should be cleared if an error was detected before issuing a new command. The device will remain in status register read mode until another command is written to the CUI.

4.7 Block Erase Suspend/Resume Command

The Block Erase Suspend command allows block erase interruption to read or program data in another blocks. Once the block erase process starts, writing the Block Erase Suspend command requests that the WSM suspend the block erase operation after a certain latency period. The device continues to output status register data when read after the Block Erase Suspend command is issued. Status Register bits SR.7 and SR.6 indicate when the block erase operation has been suspended (both will be set to "1"). Specification t_{WHRH2} defines the block erase suspend latency.

At this point, a Read Array command can be written to read data from blocks other than that which is suspended. A Program command sequence can also be issued during erase suspend to program data in other blocks. Using the Program Suspend command (see Section 4.8), a program operation can be suspended during an erase suspend. The only other valid commands while block erase is suspended are Read Status Register and Block Erase Resume.

During a block erase suspend, the chip can go into a pseudo-standby mode by taking CE# to V_{IH}, which reduces active current draw. V_{PP} must remain at $V_{PPH1/2}$ while block erase is suspended. WP# must also remain at V_{IL} or V_{IH}.

To resume the block erase operation, write the Block Erase Resume command to the CUI. This will automatically clear status register bits SR.6 and SR.7. After the Erase Resume command is written, the device automatically outputs status register data when read (see Figure 11, *Block Erase Suspend/Resume Flowchart*). Block erase cannot resume until program operations initiated during block erase suspend have completed.

4.8 Program Suspend/Resume Command

The Program Suspend command allows program interruption to read data in other flash memory locations. Once the program process starts, writing the Program Suspend command requests that the WSM suspend the program operation after a certain latency period. The device continues to output status register data when read after issuing Program Suspend command. Status register bits SR.7 and SR.2 indicate when the Program operation has been suspended (both will be set to "1"). Specification t_{WHRH1} defines the program suspend latency.

At this point, a Read Array command can be written to read data from blocks other than that which is suspended. The only other valid commands while Program is suspended are Read Status Register and Program Resume.

During a program suspend, the chip can go into a pseudo-standby mode by taking CE# to V_{IH}, which reduces active current draw. V_{PP} must remain at $V_{PPH1/2}$ while program is suspended. WP# must also remain at V_{IL} or V_{IH}.

To resume the program, write the Program Resume command to the CUI. This will automatically clear status register bits SR.7 and SR.2. After the Program Resume command is written, the device automatically outputs status register data when read (see Figure 11, *Program Suspend/Resume Flowchart*).

Table 6. Read Configuration Register Definition

RM	R	FC2	FC1	FC0	R	DOC	WC
15	14	13	12	11	10	9	8
BS	**CC**	**R**	**R**	**R**	**BL2**	**BL1**	**BL0**
7	6	5	4	3	2	1	0

	NOTES:
RCR.15 = READ MODE (RM) 0 = Synchronous Burst Reads Enabled 1 = Page-Mode Reads Enabled (Default)	Read mode configuration effects reads from main blocks. Parameter block, status register, and identifier reads support single read cycles.
RCR.14 = RESERVED FOR FUTURE ENHANCEMENTS (R)	These bits are reserved for future use. Set these bits to "0."
RCR.13–11 = FREQUENCY CONFIGURATION (FC2-0) 001 = Code 1 reserved for future use 010 = Code 2 011 = Code 3 100 = Code 4 101 = Code 5 110 = Code 6	See Section 4.9.2 for information about the frequency configuration and its effect on the initial read. Undocumented combinations of bits RCR.14–11 are reserved by Intel Corporation for future implementations and should not be used.
RCR.10 = RESERVED FOR FUTURE ENHANCEMENTS (R)	These bits are reserved for future use. Set these bits to "0."
RCR.9 = DATA OUTPUT CONFIGURATION (DOC) 0 = Hold Data for One Clock 1 = Hold Data for Two Clocks	Undocumented combinations of bits RCR.10–9 are reserved by Intel Corporation for future implementations and should not be used.
RCR.8 = WAIT CONFIGURATION (WC) 0 = WAIT# Asserted During Delay 1 = WAIT# Asserted One Data Cycle Before Delay	
RCR.7 = BURST SEQUENCE (BS) 0 = Intel Burst Order 1 = Linear Burst Order	
RCR.6 = CLOCK CONFIGURATION (CC) 0 = Burst Starts and Data Output on Falling Clock Edge 1 = Burst Starts and Data Output on Rising Clock Edge	
RCR.5–3 = RESERVED FOR FUTURE ENHANCEMENTS (R)	These bits are reserved for future use. Set these bits to "0."
RCR.2–0 = BURST LENGTH (BL2–0) 001 = 4 Word Burst 010 = 8 Word Burst 111 = Continuous Burst	In the asynchronous page mode, the burst length always equals four words. Undocumented combinations of bits RCR.2–0 are reserved by Intel Corporation for future implementations and should not be used

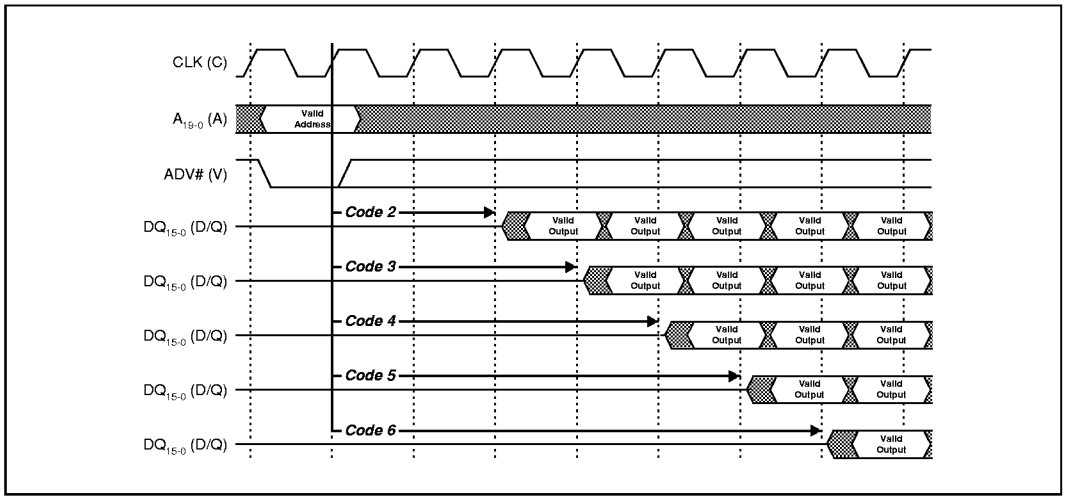


Figure 7. Frequency Configuration

Table 7. Frequency Configuration Settings(1)

Frequency Configuration Code	Input CLK Frequency		
	Product = -95		Product = -120
	V_{CC} = 3.0 V-3.6 V	V_{CC} = 2.7 V-3.6 V	V_{CC} = 2.7 V-3.6 V
1	Reserved	Reserved	Reserved
2	≤ 27 MHz	≤ 25 MHz	≤ 20 MHz
3	≤ 40 MHz	≤ 33 MHz	≤ 28 MHz
4	≤ 54 MHz	≤ 50 MHz	≤ 40 MHz
5	≤ 66 MHz	≤ 60 MHz	≤ 50 MHz
6	-	≤ 66 MHz	≤ 60 MHz

NOTE:

1. Reference Section 4.1. *Automotive Temperature Frequency Configuration Settings* for the corresponding frequency configuration codes to different input CLK frequencies.

4.9 Set Read Configuration Command

The Set Read Configuration command writes data to the read configuration register. This operation is initiated by a standard two bus cycle command sequence. The Read Configuration Setup command (60H) is written and the data to be written to the read configuration is presented, which is then followed by a second write that confirms the operation and again presents the data to be written to the read configuration register. The Read configuration register data is placed on the address bus, $A_{15:0}$,during both bus cycles and is latched on the rising edge of ADV#, CE#, or WE# (whichever occurs first). The read configuration register data sets the device's read configuration, burst order, frequency configuration, burst length and all other parameters. This command functions independently of the applied V_{PP} voltage. After executing this command, the device returns to read array mode.

4.9.1 READ CONFIGURATION

The device supports two high performance read configurations: Synchronous burst-mode and asynchronous page-mode. Bit RCR.15 in the read configuration register sets the read configuration to either synchronous burst or asynchronous page-mode. Asynchronous page-mode is the default read configuration state.

Parameter blocks, status register, and identifier only support single asynchronous and synchronous read operations.

4.9.2 FREQUENCY CONFIGURATION

The frequency configuration informs the device of the number of clocks that must elapse after ADV# is driven active before data will be available. This value is determined by the input clock frequency. See Table 7 for the specific input CLK frequency configuration code

Figure 7 illustrates data output latency from ADV# going active for different frequency configuration codes.

4.9.3 DATA OUTPUT CONFIGURATION

The output configuration determines how many clocks data will be held valid. The data hold time is configurable as either one or two clocks.

The data output configuration must be set to hold data valid for two clock cycles when the frequency configuration value is greater than 4 and burst length is greater than four words. Otherwise, its setting will depend on the system CPU's data setup requirement.

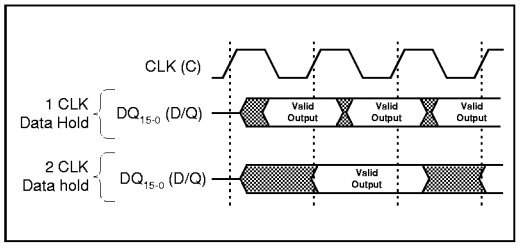


Figure 8. Output Configuration

4.9.4 WAIT# CONFIGURATION

The WAIT# configuration bit controls the behavior of the WAIT# output signal. This output signal can be set to be asserted during or one CLK cycle before an output delay when continuous burst length is enabled. Its setting will depend on the system and CPU characteristic.

4.9.5 BURST SEQUENCE

The burst sequence specifies the order in which data is addressed in synchronous burst-mode. This order is programmable as either linear or Intel burst order. The continuous burst length only supports linear burst order. The order chosen will depend on the CPU characteristic. See Table 8 for more details.

4.9.6 CLOCK CONFIGURATION

The clock configuration configures the device to start a burst cycle, output data, and assert WAIT# on the rising or falling edge of the clock. CLK flexibility helps ease 3 Volt Fast Boot Block Flash memory interface to wide range of burst CPUs.

4.9.7 BURST LENGTH

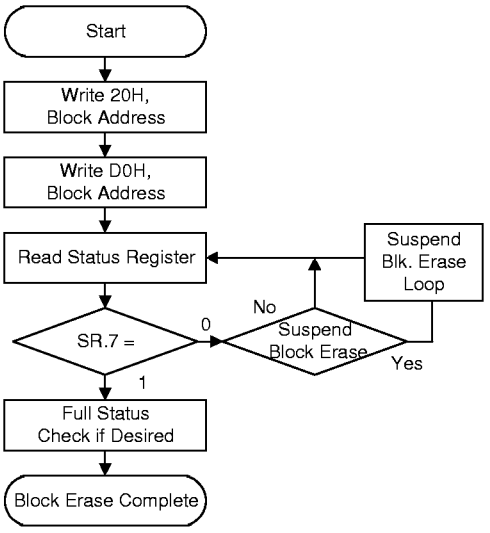
The burst length is the number of words that the device will output. The device supports burst lengths of four and eight words. In 4 or 8 word burst configuration the device will perform a wrap around type burst access (See table 8). It also supports a continuous burst mode. In continuous burst mode, the device will linearly output data until the internal burst counter reaches the end of the device's burstable address space. Bits RCR.2–0 in the read configuration register set the burst length.

4.9.7.1 Continuous Burst Length

When operating in the continuous burst mode, the flash memory may incur an output delay when the burst sequence crosses the first sixteen word boundary. The starting address dictates whether or not a delay will occur. If the starting address is aligned to a four word boundary, the delay will not be seen. If the starting address is the end of a four word boundary, the output delay will be equal to the frequency configuration setting; this is the worst case delay. The delay will only take place once during a continuous burst access, and if the burst sequence never crosses a sixteen word boundary, the delay will never happen. Using the WAIT# output pin in the continuous burst configuration, the system is informed if this output delay occurs.

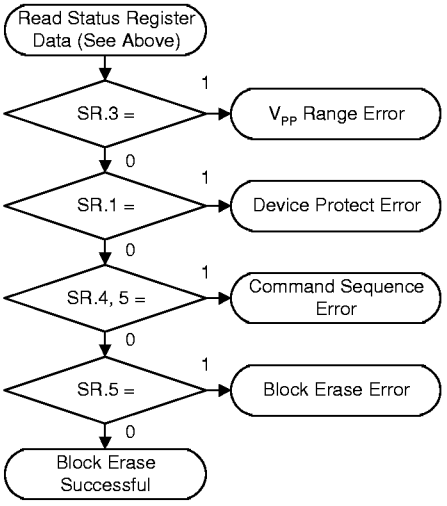
Table 8. Sequence and Burst Length

Starting Addr. (Dec)	Burst Addressing Sequence (Dec)				
	4 Word Burst Length		8 Word Burst Length		Continuous Burst
	Linear	Intel	Linear	Intel	Linear
0	0-1-2-3	0-1-2-3	0-1-2-3-4-5-6-7	0-1-2-3-4-5-6-7	0-1-2-3-4-5-6-...
1	1-2-3-0	1-0-3-2	1-2-3-4-5-6-7-0	1-0-3-2-5-4-7-6	1-2-3-4-5-6-7-...
2	2-3-0-1	2-3-0-1	2-3-4-5-6-7-0-1	2-3-0-1-6-7-4-5	2-3-4-5-6-7-8-...
3	3-0-1-2	3-2-1-0	3-4-5-6-7-0-1-2	3-2-1-0-7-6-5-4	3-4-5-6-7-8-9-...
M	M	M	M	M	M
6			6-7-0-1-2-3-4-5	6-7-4-5-2-3-0-1	6-7-8-9-10-11-12-...
7			7-0-1-2-3-4-5-6	7-6-5-4-3-2-1-0	7-8-9-10-11-12-13...
					M
14					14-15-16-17-18-19-20-...
15					15-16-17-18-19-20-21-...
					M



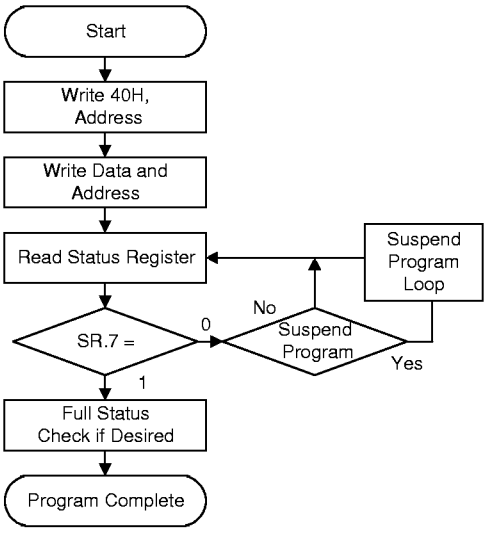
Bus Operation	Command	Comments
Write	Erase Setup	Data = 20H Addr = Within Block to Be Erased
Write	Erase Confirm	Data = D0H Addr = Within Block to Be Erased
Read		Status Register Data
Standby		Check SR.7 1 = WSM Ready 0 = WSM Busy
Repeat for subsequent block erasures. Full status check can be done after each block erase or after a sequence of block erasures. Write FFH after the last operation to place device in read array mode.		

FULL STATUS CHECK PROCEDURE



Bus Operation	Command	Comments
Standby		Check SR.3 1 = V_{PP} Error Detect
Standby		Check SR.1 1 = Device Protect Detect WP# = V_{IL}
Standby		Check SR.4, 5 Both 1 = Command Sequence Error
Standby		Check SR.5 1 = Block Erase Error
SR.5, SR.4, SR.3 and SR.1 are only cleared by the Clear Staus Register command, in cases where multiple blocks are erased before full status is checked. If an error is detected, clear the status register before attempting retry or other error recovery.		

Figure 9. Automated Block Erase Flowchart



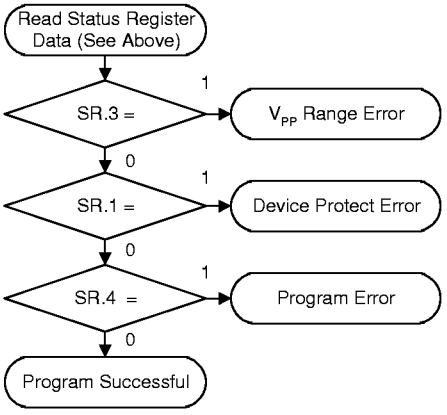
Bus Operation	Command	Comments
Write	Program Setup	Data = 40H Addr = Location to Be Written
Write	Data	Data = Data to Be Written Addr = Location to Be Written
Read		Status Register Data
Standby		Check SR.7 1 = WSM Ready 0 = WSM Busy

Repeat for subsequent byte writes.

SR full status check can be done after each byte write or after a sequence of program operations.

Write FFH after the last byte write operation to place device in read array mode.

FULL STATUS CHECK PROCEDURE

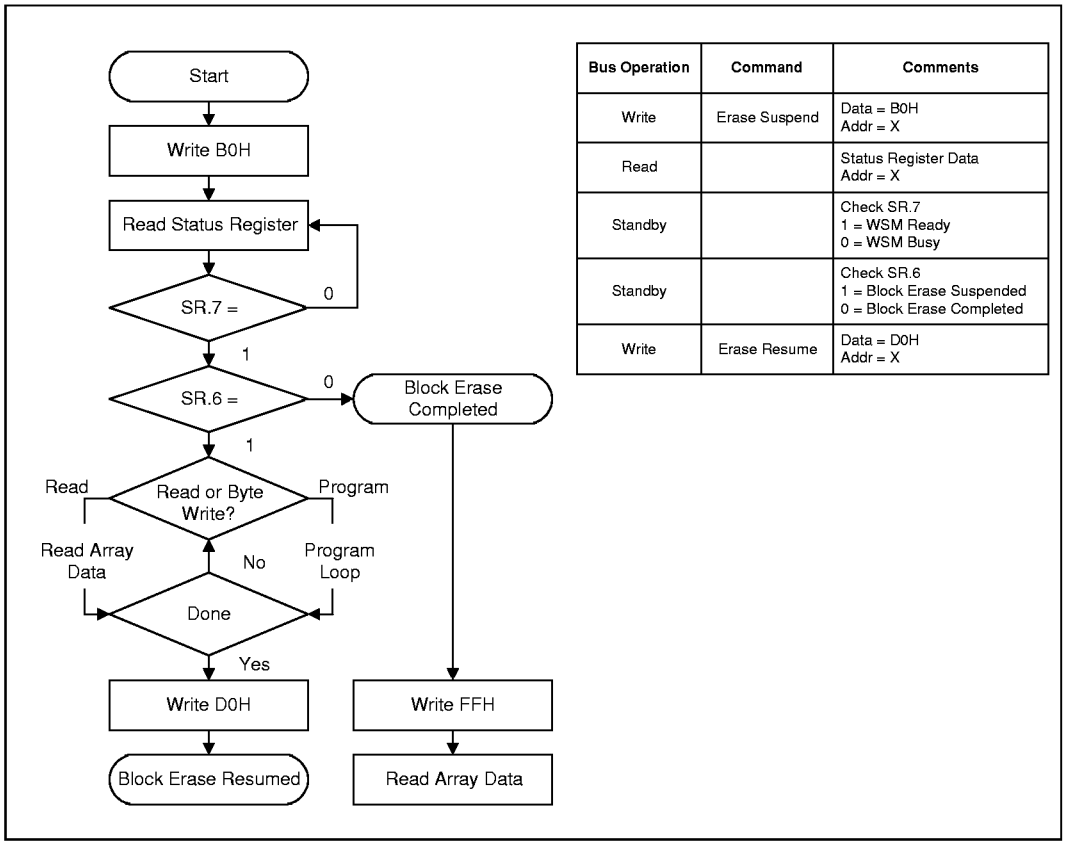


Bus Operation	Command	Comments
Standby		Check SR.3 1 = V_{PP} Error Detect
Standby		Check SR.1 1 = Device Protect Detect WP# = V_{IL}
Standby		Check SR.4 1 = Data Write Error

SR.4, SR.3 and SR.1 are only cleared by the Clear Staus Register command, in cases where multiple locations are written before full status is checked.

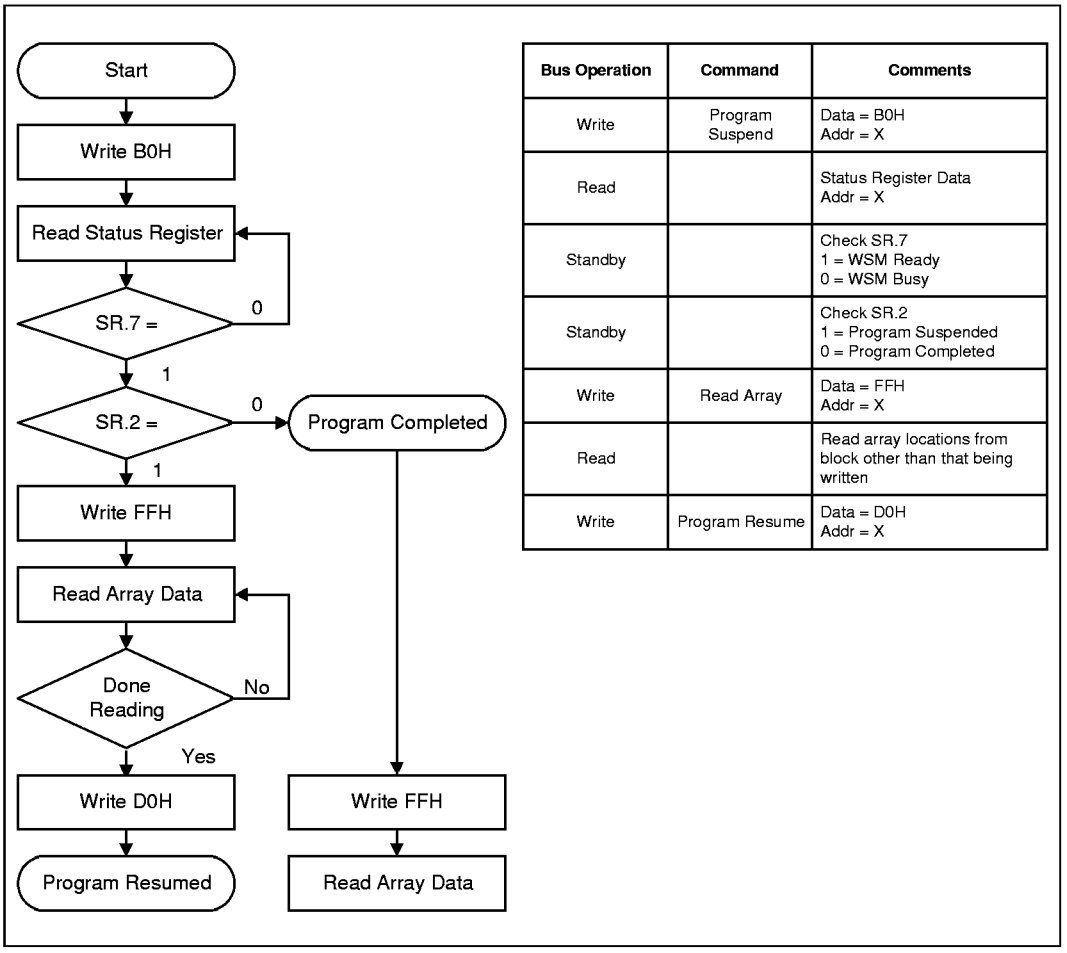
If an error is detected, clear the status register before attempting retry or other error recovery.

Figure 10. Automated Program Flowchart



Bus Operation	Command	Comments
Write	Erase Suspend	Data = B0H Addr = X
Read		Status Register Data Addr = X
Standby		Check SR.7 1 = WSM Ready 0 = WSM Busy
Standby		Check SR.6 1 = Block Erase Suspended 0 = Block Erase Completed
Write	Erase Resume	Data = D0H Addr = X

Figure 11. Block Erase Suspend/Resume Flowchart



Bus Operation	Command	Comments
Write	Program Suspend	Data = B0H Addr = X
Read		Status Register Data Addr = X
Standby		Check SR.7 1 = WSM Ready 0 = WSM Busy
Standby		Check SR.2 1 = Program Suspended 0 = Program Completed
Write	Read Array	Data = FFH Addr = X
Read		Read array locations from block other than that being written
Write	Program Resume	Data = D0H Addr = X

Figure 12. Program Suspend/Resume Flowchart

5.0 DATA PROTECTION

The 3 Volt Fast Boot Block Flash memory architecture features two hardware-lockable parameter blocks, so critical code can be kept secure while six other parameter blocks can be programmed or erased as necessary to facilitate EEROM emulation.

5.1 $V_{PP} \leq V_{PPLK}$ for Complete Protection

The V_{PP} programming voltage can be held low for complete write protection of all blocks in the flash device. When V_{PP} is below V_{PPLK}, any block erase or program operation will result in a error, prompting the corresponding status register bit (SR.3) to be set.

5.2 WP# = V_{IL} for Block Locking

The lockable blocks are locked when WP# = V_{IL}; any block erase or program operation to a locked block will result in an error, which will be reflected in the status register. For top configuration, the top two parameter blocks (blocks #37, #38 for the 16-Mbit, blocks #21, #22 for the 8-Mbit) are lockable. (Automotive temperature includes all main blocks.) For the bottom configuration, the bottom two parameter blocks (blocks #0, #1) are lockable. Unlocked blocks can be programmed or erased normally (unless V_{PP} is below V_{PPLK}).

5.3 WP# = V_{IH} for Block Unlocking

WP# controls all block locking and V_{PP} provides protection against spurious writes. Table 9 defines the write protection methods.

Table 9. Write Protection Truth Table

V_{PP}	WP#	RST#	Write Protection Provided
X	X	V_{IL}	All Blocks Locked
V_{IL}	X	V_{IH}	All Blocks Locked
$\geq V_{PPLK}$	V_{IL}	V_{IH}	Lockable Blocks Locked
$\geq V_{PPLK}$	V_{IH}	V_{IH}	All Blocks Unlocked

6.0 V_{PP} VOLTAGES

Intel's 3 Volt Fast Boot Block Flash memory family provides in-system programming and erase at 2.7 V–3.6 V (3.0 V–3.6 V for automotive temperature) V_{PP}. For customers requiring fast programming in their manufacturing environment, this family of products includes an additional high-performance 12 V programming feature.

The 12 V V_{PP} mode enhances programming performance during short period of time typically found in manufacturing processes; however, it is not intended for extended use. 12 V may be applied to V_{PP} during block erase and program operations for a maximum of 1000 cycles on the main blocks and 2500 cycles on the parameter blocks. V_{PP} may be connected to 12 V for a total of 80 hours maximum. Stressing the device beyond these limits may cause permanent damage.

7.0 POWER CONSUMPTION

While in operation, the flash device consumes active power. However, Intel® Flash devices have power savings that can significantly reduce overall system power consumption. The Automatic Power Savings (APS) feature reduces power consumption when the device is idle. When CE# is not asserted, the flash enters its standby mode, where current consumption is even lower. The combination of these features minimizes overall memory power and system power consumption.

7.1 Active Power

With CE# at a logic-low level and RST# at a logic-high level, the device is in active mode. Active power is the largest contributor to overall system power consumption. Minimizing active current has a profound effect on system power consumption, especially for battery-operated devices.

7.2 Automatic Power Savings

Automatic Power Savings (APS) provides low-power operation during active mode, allowing the flash to put itself into a low current state when not being accessed. After data is read from the memory array, the device's power consumption enters the APS mode where typical I_{CC} current is comparable to I_{CCS}. The flash stays in this static state with outputs valid until a new location is read.

7.3 Standby Power

With CE# at a logic-high level (V_{IH}) and the CUI in read mode, the flash memory is in standby mode, which disables much of the device's circuitry and substantially reduces power consumption. Outputs (DQ_0–DQ_{15}) are placed in a high-impedance state independent of the status of the OE# signal. If CE# transitions to a logic-high level during erase or program operations, the device will continue to perform the operation and consume corresponding active power until the operation is completed.

System engineers should analyze the breakdown of standby time versus active time and quantify the respective power consumption in each mode for their specific application. This will provide a more accurate measure of application-specific power and energy requirements.

7.4 Power-Up/Down Operation

The device is protected against accidental block erasure or programming during power transitions. Power supply sequencing is not required, since the device is indifferent as to which power supply, V_{PP}, V_{CC}, or V_{CCQ}, powers-up first.

7.4.1 RST# CONNECTION

The use of RST# during system reset is important with automated program/erase devices since the system expects to read from the flash memory when it comes out of reset. If a CPU reset occurs without a flash memory reset, proper CPU initialization will not occur because the flash memory may be providing status information instead of array data. Intel recommends connecting RST# to the system reset signal to allow proper CPU/flash initialization following system reset.

System designers must guard against spurious writes when V_{CC} voltages are above V_{LKO} and V_{PP} is active. Since both WE# and CE# must be low for a command write, driving either signal to V_{IH} will inhibit writes to the device. The CUI architecture provides additional protection since alteration of memory contents can only occur after successful completion of the two-step command sequences. The device is also disabled until RST# is brought to V_{IH}, regardless of the state of its control inputs. By holding the device in reset during power-up/down, invalid bus conditions during power-up can be masked, providing yet another level of memory protection.

7.4.2 V_{CC}, V_{PP} AND RST# TRANSITIONS

The CUI latches commands as issued by system software and is not altered by V_{PP} or CE# transitions or WSM actions. Its default state upon power-up, after exit from deep power-down mode or after V_{CC} transitions above V_{LKO} (Lockout voltage), is read array mode.

After any block erase or program operation is complete (even after V_{PP} transitions down to V_{PPLK}), the CUI must be reset to read array mode via the Read Array command if access to the flash memory array is desired.

7.5 Power Supply Decoupling

Flash memory's power switching characteristics require careful device de-coupling. System designers should consider three supply current issues:

1. Standby current levels (I_{CCS})
2. Active current levels (I_{CCR})
3. Transient peaks produced by falling and rising edges of CE#.

Transient current magnitudes depend on the device outputs' capacitive and inductive loading. Two-line control and proper de-coupling capacitor selection will suppress these transient voltage peaks. Each flash device should have a 0.1 µF ceramic capacitor connected between each V_{CC} and GND, and between its V_{PP} and GND. These high-frequency, inherently low-inductance capacitors should be placed as close as possible to the package leads.

7.5.1 V_{PP} TRACE ON PRINTED CIRCUIT BOARDS

Designing for in-system writes to the flash memory requires special consideration of the V_{PP} power supply trace by the printed circuit board designer. The V_{PP} pin supplies the flash memory cells current for programming and erasing. V_{PP} trace widths and layout should be similar to that of V_{CC}. Adequate V_{PP} supply traces, and de-coupling capacitors placed adjacent to the component, will decrease spikes and overshoots.

8.0 ELECTRICAL SPECIFICATIONS

NOTICE: This datasheet contains preliminary information on new products in production. The specifications are subject to change without notice. Verify with your local Intel Sales office that you have the latest datasheet before finalizing a design.

8.1 Absolute Maximum Ratings*

Temperature under Bias ..... –40 °C to +125 °C

Storage Temperature ..... –65 °C to +125 °C

Voltage On Any Pin
(except V_{CC}, V_{CCQ}, and V_{PP}) –0.5 V to +5.5 V(1)

V_{PP} Voltage ..... –0.5 V to +13.5 V(1,2,4)

V_{CC} and V_{CCQ} Voltage ..... –0.2 V to +5.0 V(1)

Output Short Circuit Current ..... 100 mA(3)

**WARNING: Stressing the device beyond the "Absolute Maximum Ratings" may cause permanent damage. These are stress ratings only. Operation beyond the "Operating Conditions" is not recommended and extended exposure beyond the "Operating Conditions" may affect device reliability.*

NOTES:

1. All specified voltages are with respect to GND. Minimum DC voltage is –0.5 V on input/output pins and –0.2 V on V_{CC} and V_{PP} pins. During transitions, this level may undershoot to –2.0 V for periods <20 ns. Maximum DC voltage on input/output pins is 5.5 V and V_{CC} and V_{CCQ} is V_{CC} + 0.5 V which, during transitions, may overshoot to V_{CC} +2.0 V for periods <20 ns.
2. Maximum DC voltage on V_{PP} may overshoot to +14.0 V for periods <20 ns.
3. Output shorted for no more than one second. No more than one output shorted at a time.
4. V_{PP} Program voltage is normally 2.7 V–3.6 V. Connection to supply of 11.4 V–12.6 V can only be done for 1000 cycles on the main blocks and 2500 cycles on the parameter blocks during program/erase. V_{PP} may be connected to 12 V for a total of 80 hours maximum.

8.2 Extended Temperature Operating Conditions

Symbol	Parameter	Notes	Min	Max	Unit
T_A	Operating Temperature		–40	+85	°C
V_{CC1}	V_{CC} Supply Voltage	1	2.7	2.85	V
V_{CC2}	V_{CC} Supply Voltage	1	2.7	3.3	V
V_{CC3}	V_{CC} Supply Voltage	1,4	2.7	3.6	V
V_{CCQ1}	I/O Voltage	1,2	1.65	2.5	V
V_{CCQ2}	I/O Voltage	1,2	1.8	2.5	V
V_{CCQ3}	I/O Voltage	1,2,4	2.7	3.6	V
V_{PPH1}	V_{PP} Supply Voltage	1	2.7	3.6	V
V_{PPH2}	V_{PP} Supply Voltage	1,4	11.4	12.6	V
Cycling	Block Erase Cycling	3	100,000		Cycles

NOTES:

1. See *DC Characteristics* tables for voltage range-specific specifications.
2. The voltage swing on the inputs, V_{IN} is required to match V_{CCQ}.
3. Applying V_{PP} = 11.4 V–12.6 V during a program or erase can only be done for a maximum of 1000 cycles on the main blocks and 2500 cycles on the parameter blocks. A hard connection to V_{PP} = 11.4 V–12.6 V is not allowed and can cause damage to the device.
4. V_{CC}, V_{CCQ}, and V_{PP1} must share the same supply when all three are between 2.7 V and 3.6 V.

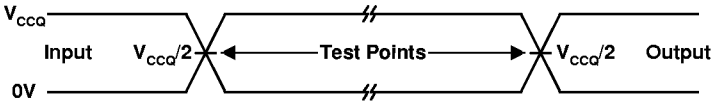
8.3 Capacitance(1)

T_A = +25 °C, f = 1 MHz

Sym	Parameter	Typ	Max	Unit	Condition
C_{IN}	Input Capacitance	6	8	pF	V_{IN} = 0.0 V
C_{OUT}	Output Capacitance	8	12	pF	V_{OUT} = 0.0 V

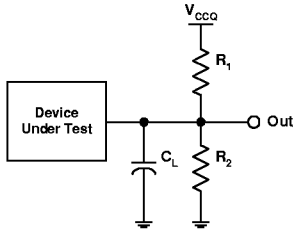
NOTE:

1. Sampled, not 100% tested.



AC test inputs are driven at V_{CCQ} min. for a Logic "1" and 0.0 V for a Logic "0." Input timing begins, and output timing ends, at $V_{CCQ}/2$. Input rise and fall times (10% to 90%) < 5 ns. Worst case speed conditions are when V_{CCQ} = 2.7 V.

Figure 13. AC Input/Output Reference Waveform for V_{CC} = 2.7 V–3.6 V



NOTE:
See table for component values.

Figure 14. AC Equivalent Testing Load Circuit

Test Configuration Component Value for Worst Case Speed Conditions

Test Configuration	C_L (pF)	R_1 (Ω)	R_2 (Ω)
2.7 V Standard Test	50	25K	25K
1.65 V Standard Test	50	16.7K	16.7K

NOTE:
C_L includes jig capacitance.

8.4 DC Characteristics—Extended Temperature[1]

Sym	Parameter	Note	V_{CC} 2.7 V–3.6 V, V_{CCQ} 2.7 V–3.6 V Typ	Max	V_{CC} 2.7 V–2.85 V, V_{CCQ} 1.65 V–2.5 V Typ	Max	V_{CC} 2.7 V–3.3 V, V_{CCQ} 1.8 V–2.5 V Typ	Max	Unit	Test Conditions
I_{LI}	Input Load Current	6		± 1		± 1		± 1	µA	$V_{CC} = V_{CC}Max$ $V_{CCQ} = V_{CCQ}Max$ $V_{IN} = V_{CCQ}$ or GND
I_{LO}	Output Leakage Current	6		± 10		± 10		± 10	µA	$V_{CC} = V_{CC}Max$ $V_{CCQ} = V_{CCQ}Max$ $V_{IN} = V_{CCQ}$ or GND
	Output Leakage Current for WAIT#			± 25		± 25		± 25		
I_{CCS}	V_{CC} Standby Current	6	30	50	20	50	150	250	µA	$V_{CC} = V_{CC}Max$ CE# = RP# = V_{CC} or during Program/ Erase Suspend WP# = V_{CC} or GND
I_{CCR}	V_{CC} Read Current	6	45	60	30	45	40	55	mA	Asynchronous t_{AVAV} = Min $V_{IN} = V_{IH}$ or V_{IL}
			45	60	30	45	40	55	mA	Synchronous CLK = 33 MHz CE# = V_{IL} OE# = V_{IH} Burst length = 4 Word
I_{CCW}	V_{CC} Program Current	3,6	8	20	8	20	8	20	mA	$V_{PP} = V_{PP1, 2}$ Program in Progress
I_{CCE}	V_{CC} Erase Current	3,6	8	20	8	20	8	20	mA	$V_{PP} = V_{PP1, 2}$ Erase in Progress
I_{PPR}	V_{PP} Read Current		2	±15	2	±15	2	±15	µA	$V_{PP} \leq V_{CC}$
		3	50	200	50	200	50	200	µA	$V_{PP} > V_{CC}$
I_{PPW}	V_{PP} Program Current	3,4	10	35	10	35	10	35	mA	$V_{PP} = V_{PP1}$ Program in Progress
			2	10	2	10	2	10	mA	$V_{PP} = V_{PP2}$ Program in Progress
I_{PPE}	V_{PP} Erase Current	3,4	12	25	13	25	13	25	mA	$V_{PP} = V_{PP1}$ Program in Progress
			8	25	8	25	8	25	mA	$V_{PP} = V_{PP2}$ Program in Progress
I_{PPES} I_{PPWS}	V_{PP} Erase Suspend Current	3	50	200	50	200	50	200	µA	$V_{PP} = V_{PP1, 2}$ Program or Erase Suspend in Progress

8.4 DC Characteristics—Extended Temperature (Continued)

Sym	Parameter	Note	V_{CC} 2.7 V–3.6 V / V_{CCQ} 2.7 V–3.6 V Min	Max	V_{CC} 2.7 V–2.85 V / V_{CCQ} 1.65 V–2.5 V Min	Max	V_{CC} 2.7 V–3.3 V / V_{CCQ} 1.8 V–2.5 V Min	Max	Unit	Test Conditions
V_{IL}	Input Low Voltage		–0.4	0.22 * Vcc	–0.2	0.2	–0.2	0.2	V	
V_{IH}	Input High Voltage		2.0	5.5	V_{CCQ} – 0.2	V_{CCQ} + 0.2	V_{CCQ} – 0.2	V_{CCQ} + 0.2	V	
V_{OL}	Output Low Voltage			0.10	-0.10	0.10	-0.10	0.10	V	$V_{CC} = V_{CC}$Min $V_{CCQ} = V_{CCQ}$Min I_{OL} = 100 µA
V_{OH}	Output High Voltage		V_{CCQ} – 0.1		V_{CCQ} – 0.1		V_{CCQ} – 0.1		V	$V_{CC} = V_{CC}$Min $V_{CCQ} = V_{CCQ}$Min I_{OH} = –100 µA
V_{PPLK}	V_{PP} Lock-Out Voltage	2	1.5	1.5		1.5		1.5	V	Complete Write Protection
V_{PP1}	V_{PP} during Program and Erase Operations	2	2.7	3.6					V	
V_{PP2}		2			2.7	2.85			V	
V_{PP3}		2					2.7	3.3	V	
V_{PP4}		2,5	11.4	12.6	11.4	12.6	11.4	12.6	V	
V_{LKO}	V_{CC} Prog/Erase Lock Voltage		1.5		1.5		1.5		V	
V_{LKO2}	V_{CCQ} Prog/Erase Lock Voltage		1.2		1.2		1.2		V	

NOTES:

1. All currents are in RMS unless otherwise noted. Typical values at normal V_{CC}, T = +25 °C.
2. I_{CCES} is specified with device deselected. If device is read while in erase suspend, current draw is sum of I_{CES} and I_{CCR}.
3. Erases and program operations are inhibited when $V_{PP} \le V_{PPLK}$, and not guaranteed outside the valid V_{PP} ranges of V_{PPH1} and V_{PPH2}.
4. Sampled, not 100% tested.
5. Automatic Power Savings (APS) reduces I_{CCR} to approximately standby levels, in static operation.
6. Applying V_{PP} = 11.4 V–12.6 V during program/erase can only be done for a maximum of 1000 cycles on the main blocks and 2500 cycles on the parameter blocks. V_{PP} may be connected to 12 V for a total of 80 hours maximum.
7. The specification is the sum of V_{CC} and V_{CCQ} currents.

8.5 AC Characteristics—Read-Only Operations[1,5]–Extended Temperature

#	Sym	Parameter	Product	–95				–120		Unit
			V_{CC}	3.0 V–3.6 V		2.7 V–3.6 V		2.7 V–3.6 V		
			Notes	Min	Max	Min	Max	Min	Max	
R1	t_{CLK}	CLK Period		15		15		15		ns
R2	$t_{CH}(t_{CL})$	CLK High (Low) Time		2.5		2.5		2.5		ns
R3	t_{CHCL}	CLK Fall (Rise) Time			5		5		5	ns
R4	t_{AVCH}	Address Valid Setup to CLK		7		7		7		ns
R5	t_{VLCH}	ADV# Low Setup to CLK		7		7		7		ns
R6	t_{ELCH}	CE# Low Setup to CLK		7		7		7		ns
R7	t_{CHQV}	CLK to Output Delay			14		16		23	ns
R8	t_{CHQX}	Output Hold from CLK	6	5		5		5		ns
R9	t_{CHAX}	Address Hold from CLK	3	10		10		10		ns
R10	t_{CHTL}	CLK to WAIT# delay			14		16		23	ns
R11	t_{AVVH}	Address Setup to ADV# High		10		10		10		ns
R12	t_{ELVH}	CE# Low to ADV# High		10		10		10		ns
R13	t_{AVQV}	Address to Output Delay			90		95		120	ns
R14	t_{ELQV}	CE# Low to Output Delay	2		90		95		120	ns
R15	t_{VLQV}	ADV# Low to Output Delay			90		95		120	ns
R16	t_{VLVH}	ADV# Pulse Width Low		10		10		10		ns
R17	t_{VHVL}	ADV# Pulse Width High		10		10		10		ns
R18	t_{VHAX}	Address Hold from ADV# High		3		3		3		ns
R19	t_{APA}	Page Address Access Time			25		27		35	ns
R20	t_{GLQV}	OE# Low to Output Delay			25		25		30	ns
R21	t_{PHQV}	RST# High to Output Delay			600		600		600	ns
R22	t_{EHQZ} t_{GHQZ}	CE# or OE# High to Output in High Z, Whichever Occurs First	4		20		20		20	ns
R23	t_{OH}	Output Hold from Address, CE#, or OE# Change, Whichever Occurs First	4	0		0		0		ns

NOTES:

1. See *AC Input/Output Reference Waveform*, (figure 13), for timing measurements and maximum allowable input slew rate.
2. OE# may be delayed up to t_{ELQV}–t_{GLQV} after the falling edge of CE# without impact on t_{ELQV}.
3. Address hold in synchronous burst-mode is defined as t_{CHAX} or t_{VHAX}, whichever timing specification is satisfied first.
4. Sampled, not 100% tested.
5. Data bus voltage must be less than or equal to V_{CCQ} when a read operation is initiated to guarantee AC specifications.
6. Tested at worst case processor conditions.

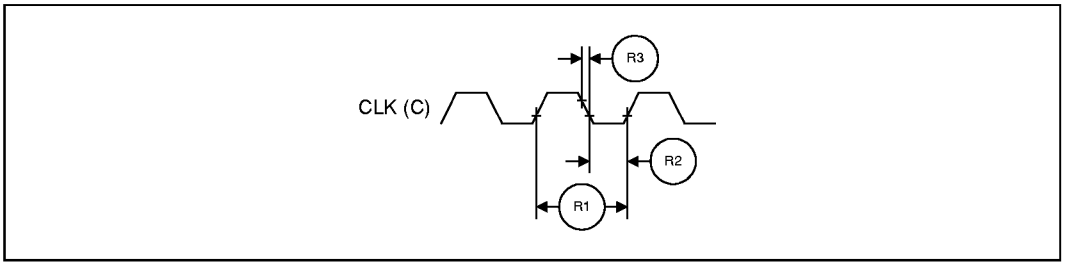


Figure 15. AC Waveform for CLK Input

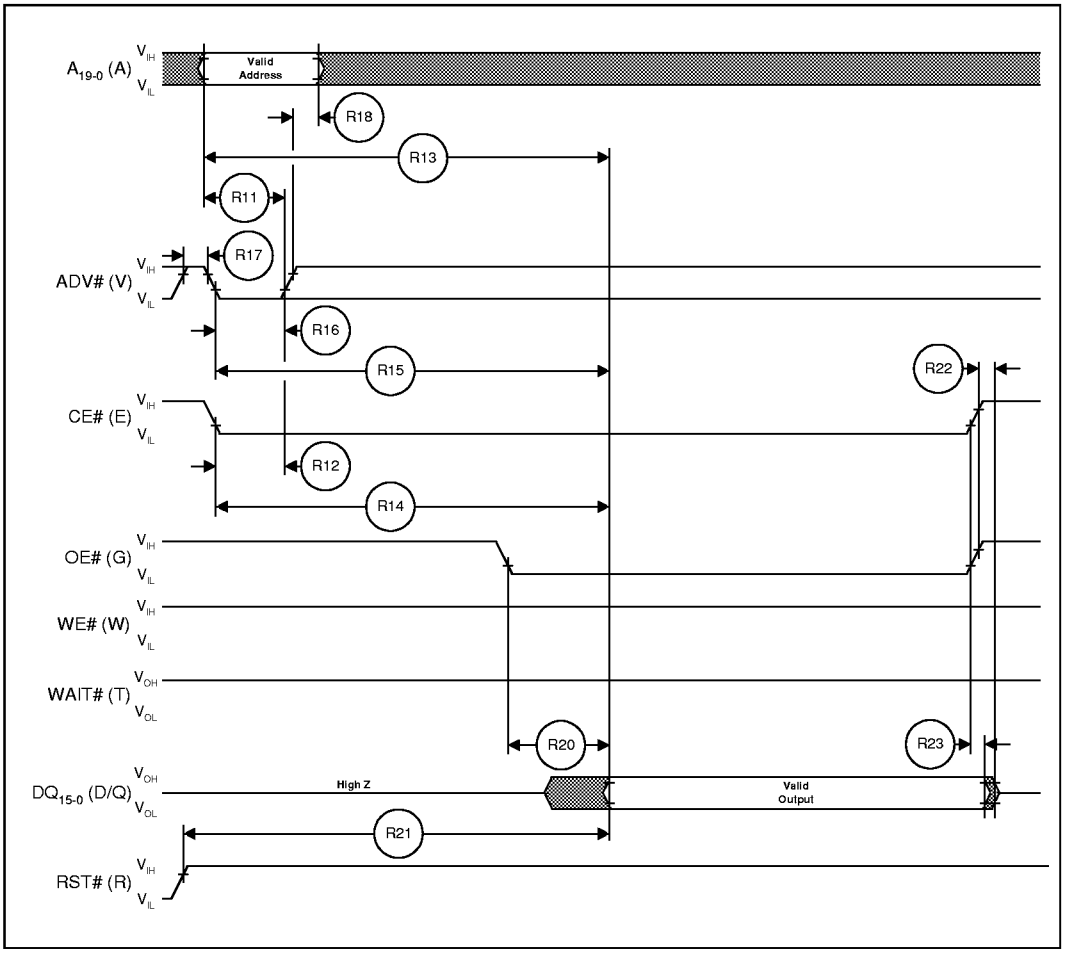


Figure 16. AC Waveform for Single Asynchronous Read Operation from Parameter Blocks, Status Register, Identifier Codes

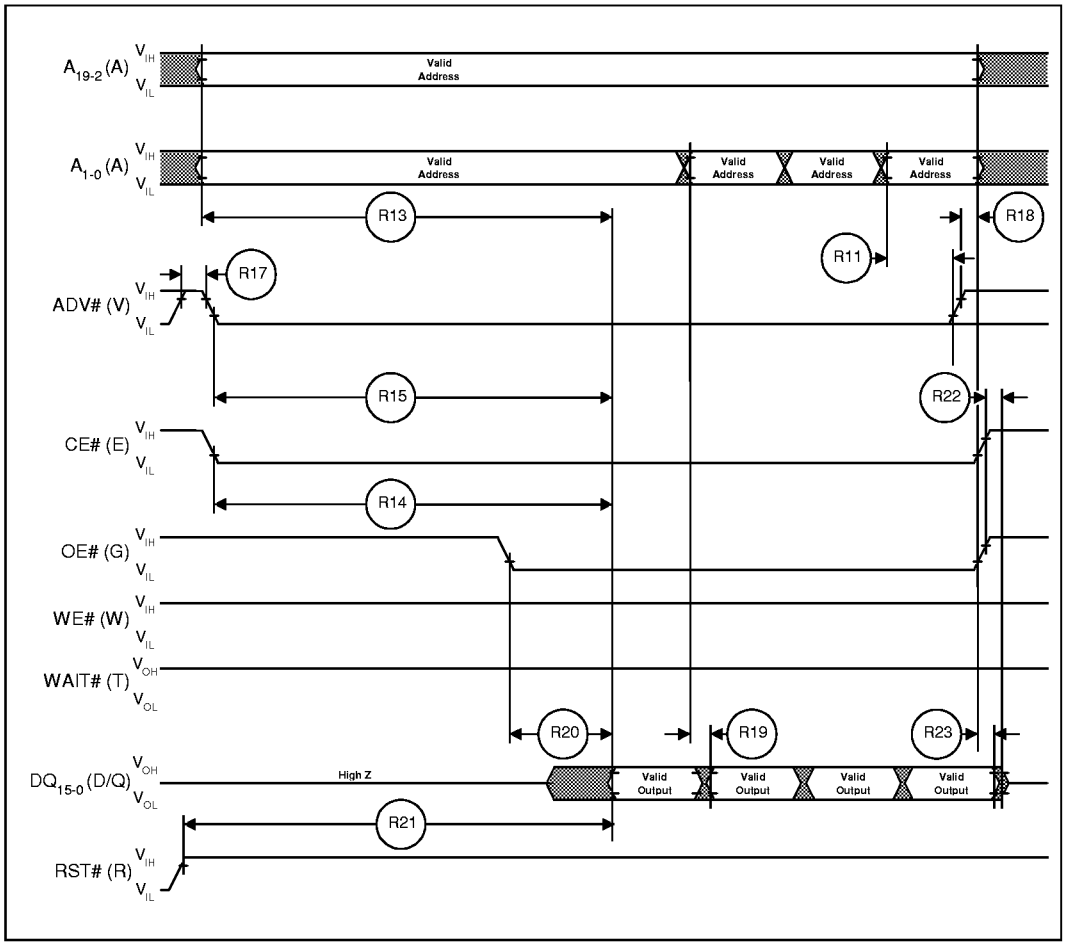
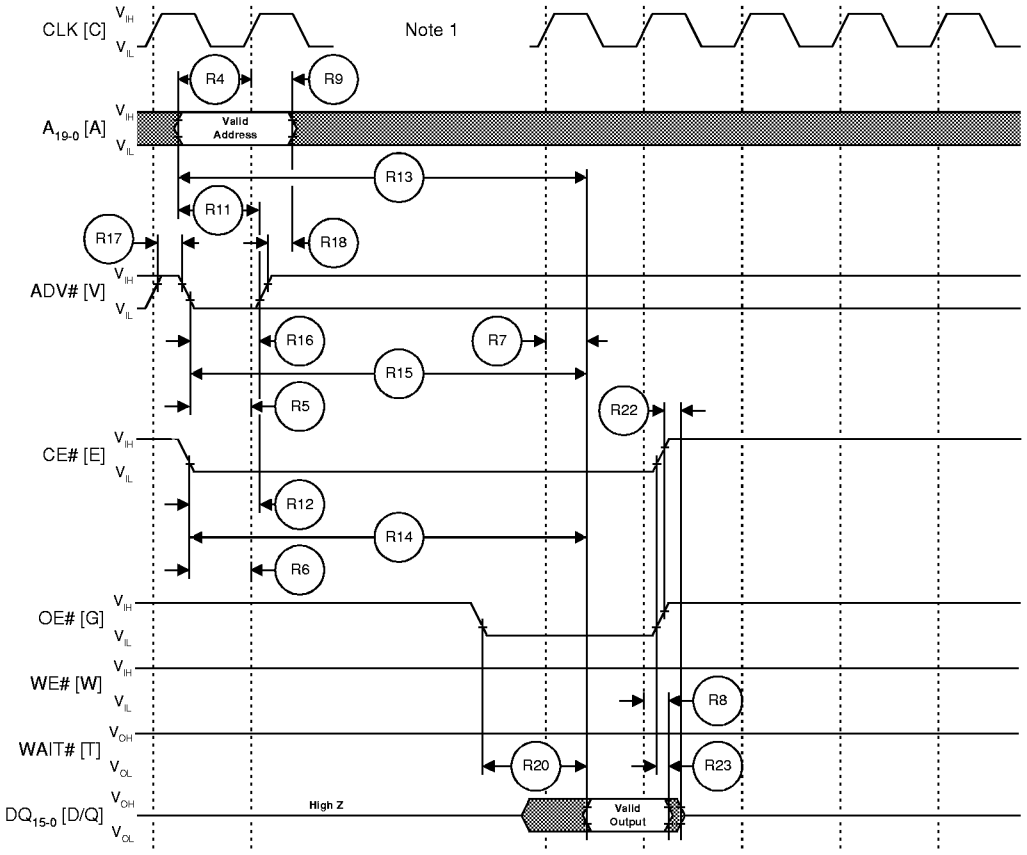


Figure 17. AC Waveform for Asynchronous Page-Mode Read Operations from Main Blocks

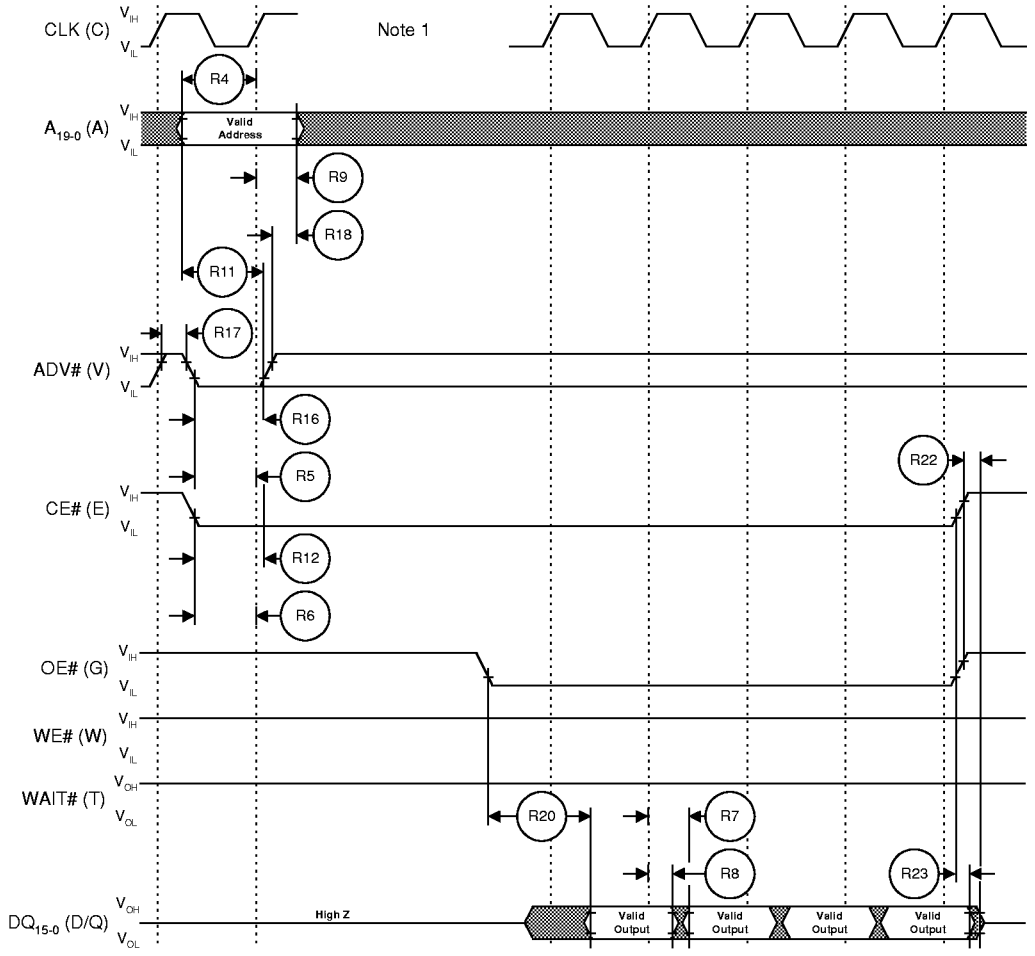


NOTE:

1. Depending upon the frequency configuration code value in the read configuration register, insert clock cycles:
   - Frequency Configuration 2 insert two clock cycles
   - Frequency Configuration 3 insert three clock cycles
   - Frequency Configuration 4 insert four clock cycles
   - Frequency Configuration 5 insert five clock cycles
   - Frequency Configuration 6 insert six clock cycles

   See Section 4.9.2 for further information about the frequency configuration and its effect on the initial read.

Figure 18. AC Waveform for Single Synchronous Read Operations from Parameter Blocks, Status Register, Identifier Codes

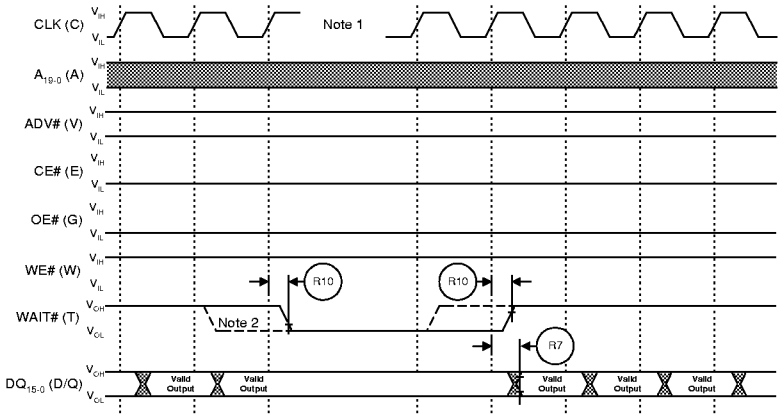


NOTE:

1. Depending upon the frequency configuration code value in the read configuration register, insert clock cycles:
   - Frequency Configuration 2 insert two clock cycles
   - Frequency Configuration 3 insert three clock cycles
   - Frequency Configuration 4 insert four clock cycles
   - Frequency Configuration 5 insert five clock cycles
   - Frequency Configuration 6 insert six clock cycles

   See Section 4.9.2 for further information about the frequency configuration and its effect on the initial read.

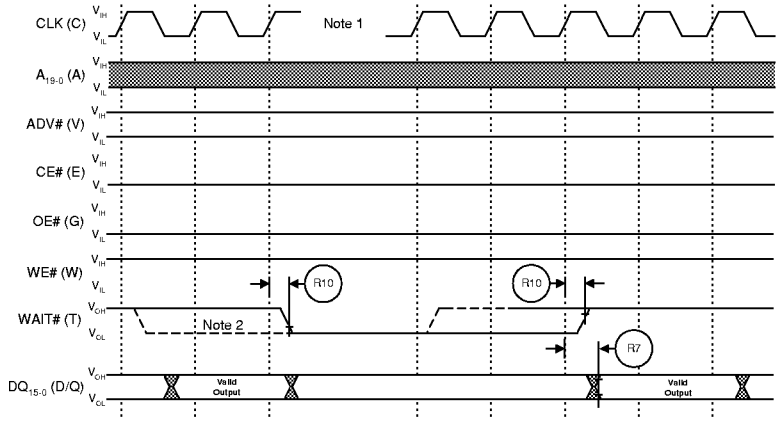
Figure 19. AC Waveform for Synchronous Burst Read Operations, Four Word Burst Length, from Main Blocks



NOTES:

1. This delay will only occur when burst length is configured as continuous. See Section 4.9.7 for furtherinformation about burst length configuration.
2. WAIT# is configurable. It can be set to assert during or one CLK cycle before an output delay. See Section 4.9.4 for further information about the behavior of WAIT#.

Figure 20. AC Waveform for Continuous Burst Read, Showing an Output Delay with Data Output Configuration Set to One Clock



NOTES:

1. This delay will only occur when burst length is configured as continuous. See Section 4.9.7 forfurther information about burst length configuration.
2. WAIT# is configurable. It can be set to assert during or one CLK cycle before an output delay. See Section 4.9.4 for further information about the behavior of WAIT#.

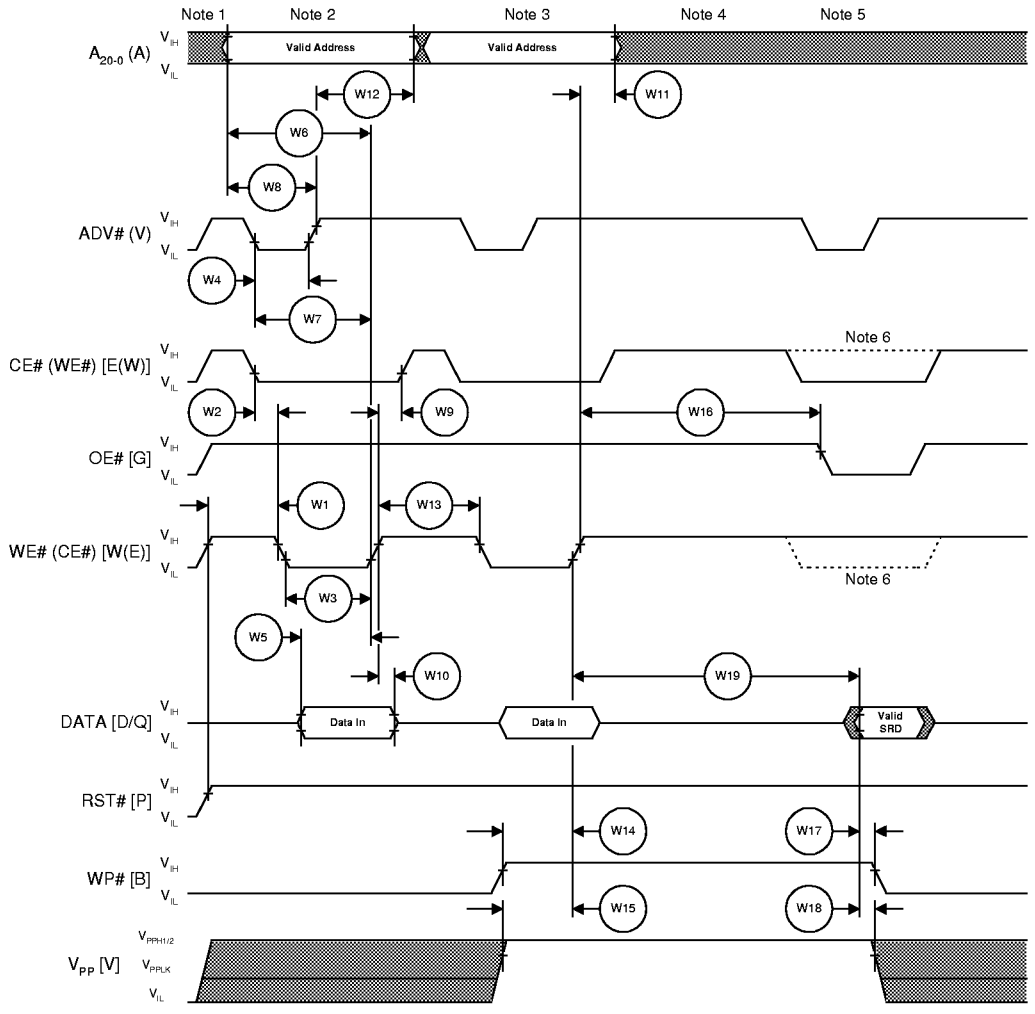
Figure 21. AC Waveform for Continuous Burst Read, Showing an Output Delay with Data Output Configuration Set to Two Clocks

8.6 AC Characteristics—Write Operations[1, 2]—Extended Temperature

#	Sym	Parameter	Valid for All Speed and Voltage Combinations			Unit
			Notes	Min	Max	
W1	t_{PHWL} (t_{PHEL})	RST# High Recovery to WE# (CE#) Going Low	3	600		µs
W2	t_{ELWL} (t_{WLEL})	CE# (WE#) Setup to WE# (CE#) Going Low	6	0		ns
W3	t_{WP}	Write Pulse Width	6	75		ns
W4	t_{VLVH}	ADV# Pulse Width		10		ns
W5	t_{DVWH} (t_{DVEH})	Data Setup to WE# (CE#) Going High	4	70		ns
W6	t_{AVWH} (t_{AVEH})	Address Setup to WE# (CE#) Going High	4	75		ns
W7	t_{VLEH} (t_{VLWH})	ADV# Setup to WE# (CE#) Going High		75		ns
W8	t_{AVVH}	Address Setup to ADV# Going High		10		ns
W9	t_{WHEH} (t_{EHWH})	CE# (WE#) Hold from WE# (CE#) High		0		ns
W10	t_{WHDX} (t_{EHDX})	Data Hold from WE# (CE#) High		0		ns
W11	t_{WHAX} (t_{EHAX})	Address Hold from WE# (CE#) High		0		ns
W12	t_{VHAX}	Address Hold from ADV# Going High		3		ns
W13	t_{WPH}	Write Pulse Width High	7	20		ns
W14	t_{BHWH} (t_{BHEH})	WP# Setup to WE# (CE#) Going High	3	200		ns
W15	t_{VPWH} (t_{VPEH})	V_{PP} Setup to WE# (CE#) Going High	3	200		ns
W16	t_{WHGL} (t_{EHGL})	Write Recovery before Read		0		ns
W17	t_{QVBL}	WP# Hold from Valid SRD	3,5	0		ns
W18	t_{QVVL}	V_{PP} Hold from Valid SRD	3,5	0		ns

NOTES:

1. See *AC Input/Output Reference Waveform*, (Figure 13), for timing measurements and maximum allowable input slew rate.
2. A write operation can be initiated and terminated with either CE# or WE#.
3. Sampled, not 100% tested.
4. Refer to Table 3 for valid A_{IN} and D_{IN} for block erase or program.
5. V_{PP} should be held at $V_{PPH1/2}$ until determination of block erase or program success.
6. Write pulse width (t_{WP}) is defined from CE# or WE# going low (whichever goes low last) to CE# or WE# going high (whichever goes high first). Hence, $t_{WP} = t_{WLWH} = t_{ELEH} = t_{WLEH} = t_{ELWH}$.
7. Write pulse width high (t_{WPH}) is defined from CE# or WE# going high (whichever goes high first) to CE# or WE# going low (whichever goes low last). Hence, $t_{WPH} = t_{WHWL} = t_{EHEL} = t_{WHEL} = t_{EHWL}$.



NOTES:

1. V_{CC} power-up and standby.
2. Write block erase or program setup.
3. Write block erase confirm or valid address and data.
4. Automated erase or program delay.
5. Read status register data.
6. For read operations, OE# and CE# must be driven active, and WE# de-asserted.

Figure 22. AC Waveform for Write Operations

8.7 AC Characteristics—Reset Operation—Extended Temperature

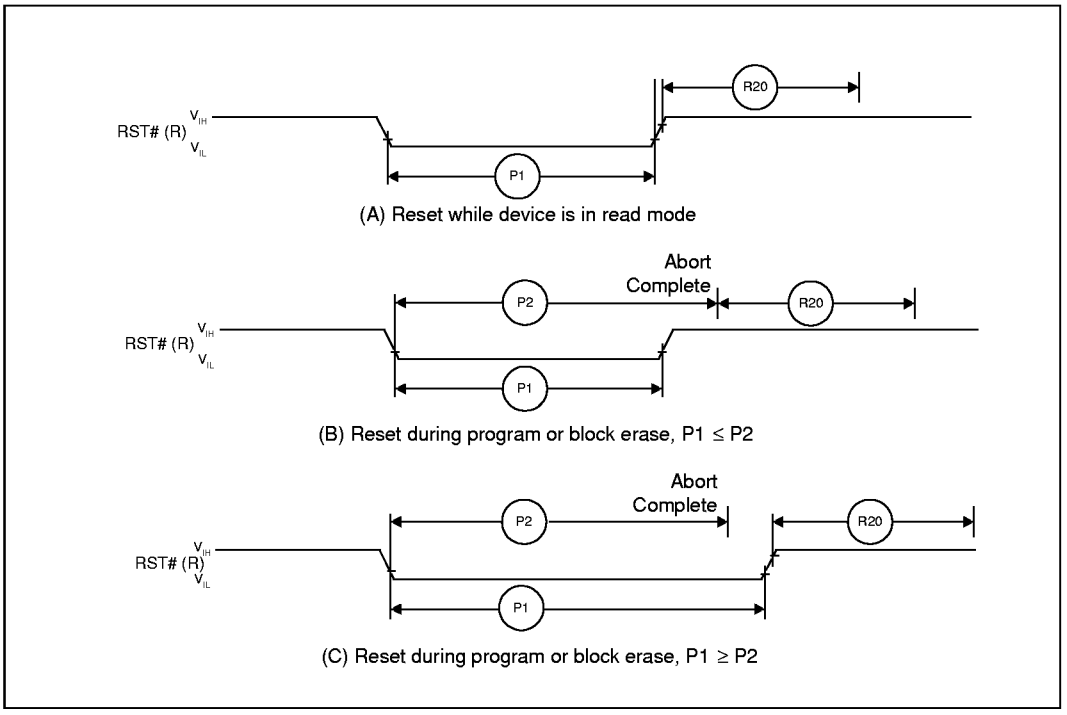


Figure 23. AC Waveform for Reset Operation

Table 10. Reset Specifications

#	Symbol	Parameter	Notes	Min	Max	Unit
P1	t_{PLPH}	RST# Low to Reset During Read (If RST# is tied to V_{CC}, this specification is not applicable)	2,4	100		ns
P2	t_{PLRH}	RST# Low to Reset during Block Erase or Program	3,4		22	µs

NOTES:

1. These specifications are valid for all product versions (packages and speeds).
2. If t_{PLPH} is < 100 ns the device may still reset but this is not guaranteed.
3. If RST# is asserted while a block erase or word program operation is not executing, the reset will complete within 100 ns.
4. Sampled, but not 100% tested.

8.8 Extended Temperature Block Erase And Program Performance[3, 4, 5]

#	Sym	Parameter	Notes	2.7 V V_{PP}		12 V V_{PP}		Unit
				Typ[1]	Max	Typ[1]	Max	
W19	t_{WHRH1}, t_{EHRH1}	Program Time	2	23.5	200	8	185	µs
		Block Program Time (Parameter)	2	0.10	0.30	0.03	0.10	sec
		Block Program Time (Main)	2	0.8	2.4	0.24	0.8	sec
	t_{WHRH2}, t_{EHRH2}	Block Erase Time (Parameter)	2	1	4	0.8	4	sec
		Block Erase Time (Main)	2	1.8	5	1.1	5	sec
	t_{WHRH5}, t_{EHRH5}	Program Suspend Latency		6	10	5	10	µs
	t_{WHRH6}, t_{EHRH6}	Erase Suspend Time		13	20	10	12	µs

NOTES:

1. Typical values measured at T_A = +25 °C and nominal voltages. Subject to change based on device characterization.
2. Excludes system-level overhead.
3. These performance numbers are valid for all speed versions.
4. Sampled, but not 100% tested.
5. Reference the *AC Waveform for Write Operations* Figure 22.

8.9 Automotive Temperature Operating Conditions

Except for the specifications given in this section, all DC and AC characteristics are identical to those listed in the extended temperature specifications. See Section 8.2 for extended temperature specifications.

Symbol	Parameter	Notes	Min	Max	Unit
T_A	Operating Temperature		-40	+125	°C
V_{CC1}	V_{CC} Supply Voltage	1	3.0	3.6	V
V_{CCQ1}	I/O Voltage	1,2	3.0	3.6	V
V_{PPH1}	V_{PP} Supply Voltage	1	3.0	3.6	V
V_{PPH2}	V_{PP} Supply Voltage	1,3	11.4	12.6	V
Cycling	Parameter Block Erase Cycling		30,000		Cycles
	Main Block Erase Cycling		1,000		Cycles

NOTES:

1. See DC Characteristics tables for voltage range-specific specifications.
2. The voltage swing on the inputs, V_{IN} is required to match V_{CCQ}.
3. Applying V_{PP} = 11.4 V–12.6 V during a program/erase can only be done for a maximum of 1000 cycles on the main and parameter blocks. A hard connection to V_{PP} = 11.4 V–12.6 V is not allowed and can cause damage to the device.

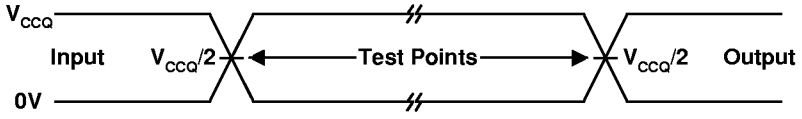
8.10 Capacitance(1)

T_A = +25°C, f = 1 MHz

Sym	Parameter	Typ	Max	Unit	Condition
C_{IN}	Input Capacitance	6	8	pF	V_{IN} = 0.0 V
C_{OUT}	Output Capacitance	8	12	pF	V_{OUT} = 0.0 V

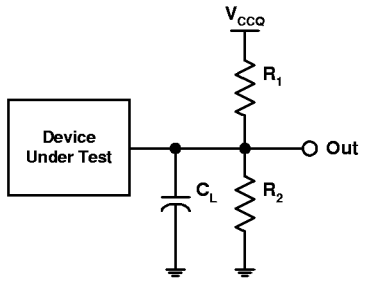
NOTE:

1. Sampled, not 100% tested.



AC test inputs are driven at 3.0 V for a Logic "1" and 0.0 V for a Logic "0." Input timing begins, and output timing ends, at V_{CCQ}/2. Input rise and fall times (10% to 90%) < 5 ns. Worst case speed conditions are when V_{CCQ} = 3.0 V.

Figure 24. AC Input/Output Reference Waveform for V_{CC} = 3.3 V ± 0.3 V



NOTE:
See table for component values.

Figure 25. AC Equivalent Testing Load Circuit

Test Configuration Component Value for Worst Case Speed Conditions

Test Configuration	C_L (pF)	R_1 (Ω)	R_2 (Ω)
3 V Auto Test	80	25K	25K
3 V Standard Test	50	25K	25K

NOTE:
C_L includes jig capacitance.

8.11 DC Characteristics(1) –Automotive Temperature

Sym	Parameter	Note	Typ	Max	Unit	Test Condition	
I_{CCS}	V_{CC} Standby Current	2,6	40	60	µA	$V_{CC} = V_{CC}$ Max $V_{CCQ} = V_{CCQ}$ Max CE# = RST# = V_{IH}	
I_{CCR}	V_{CC} Read Current	4,6	45	60	mA	Asynchronous t_{AVAV} = Min	$V_{CC} = V_{CC}$ Max $V_{CCQ} = V_{CCQ}$ Max $V_{IN} = V_{IH}$ or V_{IL}
			45	60	mA	Synchronous CLK = 22 MHz	CE# = V_{IL} OE# = V_{IH} Burst length = 1
I_{CCW}	V_{CC} Program Current	3,5,7	8	20	mA	$V_{PP} = V_{PPH1}$ (3.0 V–3.6 V) Program in progress	
			8	20	mA	$V_{PP} = V_{PPH2}$ (11.4 V–12.6 V) Program in progress	
I_{CCE}	V_{CC} Block Erase Current	3,5,7	8	20	mA	$V_{PP} = V_{PPH1}$ (3.0 V–3.6 V) Block erase in progress	
			8	20	mA	$V_{PP} = V_{PPH2}$ (11.4 V–12.6 V) Block erase in progress	
I_{PPW}	V_{PP} Program Current	3,5,7	15	40	mA	$V_{PP} = V_{PPH1}$ (3.0 V–3.6 V) Program in progress	
			10	25	mA	$V_{PP} = V_{PPH2}$ (11.4 V–12.6 V) Program in progress	
I_{PPE}	V_{PP} Block Erase Current	3,5,7	13	25	mA	$V_{PP} = V_{PPH1}$ (3.0 V–3.6 V) Block erase in progress	
			8	25	mA	$V_{PP} = V_{PPH2}$ (11.4 V–12.6 V) Block erase in progress	

NOTES:

1. All currents are in RMS unless otherwise noted. Typical values at normal V_{CC}, T = +25 °C.
2. Erases and program operations are inhibited when $V_{PP} \le V_{PPLK}$, and not guaranteed outside the valid V_{PP} ranges of V_{PPH1} and V_{PPH2}.
3. Sampled, not 100% tested.
4. Automatic Power Savings (APS) reduces I_{CCR} to approximately standby levels, in static operation.
5. 12 V (11.4 V–12.6 V) can only be applied to V_{PP} for a maximum of 80 hours over the lifetime of the device. V_{PP} should not be permanently tied to 12 V.
6. The specification is the sum of V_{CC} and V_{CCQ} currents.

8.12 AC Characteristics—Read-Only Operations[1] –Automotive Temperature

#	Sym	Parameter	Product	–115		–125		Unit
			V_{CC}	3.0 V–3.6 V		3.0 V–3.6 V		
			Notes	Min	Max	Min	Max	
R1	t_{CLK}	CLK Period		15		15		ns
R2	t_{CH} (t_{CL})	CLK High (Low) Time		2.5		2.5		ns
R3	t_{CHCL} (t_{CLCH})	CLK Fall (Rise) Time			5		5	ns
R4	t_{AVCH}	Address Valid Setup to CLK		10		14		ns
R5	t_{VLCH}	ADV# Low Setup to CLK		10		14		ns
R6	t_{ELCH}	CE# Low Setup to CLK		10		14		ns
R7	t_{CHQV}	CLK to Output Delay			19		30	ns
R8	t_{CHQX}	Output Hold from CLK		5		5		ns
R9	t_{CHAX}	Address Hold from CLK	3	10		10		ns
R10	t_{CHTL} (t_{CHTH})	CLK to WAIT# delay	4		19		30	ns
R11	t_{AVVH}	Address Setup to ADV# Going High		12		16		ns
R12	t_{ELVH}	CE# Low to ADV# Going High		12		16		ns
R13	t_{AVQV}	Address to Output Delay			115		125	ns
R14	t_{ELQV}	CE# Low to Output Delay	2		115		125	ns
R15	t_{VLQV}	ADV# Low to Output Delay			115		125	ns
R16	t_{VLVH}	ADV# Pulse Width Low		12		14		ns
R17	t_{VHVL}	ADV# Pulse Width High		12		14		ns
R18	t_{VHAX}	Address Hold from ADV# Going High	3	3		3		ns
R19	t_{APA}	Page Address Access Time			35		35	ns
R20	t_{GLQV}	OE# Low to Output Delay			40		40	ns
R21	t_{RHQV}	RST# High to Output Delay			600		600	ns
R22	t_{EHQZ} t_{GHQZ}	CE# or OE# High to Output in High Z, Whichever Occurs First	4		30		30	ns
R23	t_{OH}	Output Hold from Address, CE#, or OE# Change, Whichever Occurs First	4	0		0		ns

NOTES:
1. See *AC Input/Output Reference Waveform*, (figure 13), for timing measurements and maximum allowable input slew rate.
2. OE# may be delayed up to t_{ELQV}–t_{GLQV} after the falling edge of CE# without impact on t_{ELQV}.
3. Address hold in synchronous burst-mode is defined as t_{CHAX} or t_{VHAX}, whichever timing specification is satisfied first.
4. Sampled, not 100% tested.
5. Data bus voltage must be less than or equal to V_{CCQ} when a read operation is initiated to guarantee AC specifications
6. Tested at worst case processor conditions.

8.13 Automotive Temperature Frequency Configuration Settings

Table 11. Frequency Configuration Settings for Automotive Temperature Components

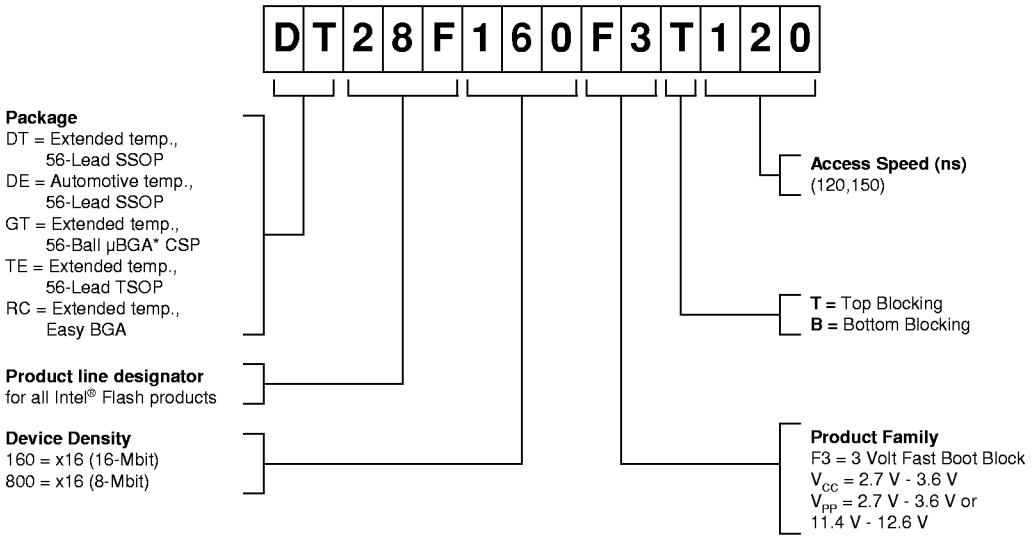
Frequency Configuration Code	Input CLK Frequency
1	Reserved
2	≤ 25 MHz
3	≤ 33 MHz
4	≤ 40 MHz
5	≤ 50 MHz
6	≤ 66 MHz

8.14 Automotive Temperature Block Erase and Program Performance(3,4,5)

#	Sym	Parameter	Notes	3.3 V V_{PP}		12 V V_{PP}		Unit
				Typ(1)	Max	Typ(1)	Max	
W19	t_{WHRH1}, t_{EHRH1}	Program Time	2	23.5	TDB	8	TDB	µs
		Block Program Time (Parameter)	2	0.10	TDB	0.03	TDB	sec
		Block Program Time (Main)	2	0.8	TDB	0.24	TDB	sec
	t_{WHRH2}, t_{EHRH2}	Block Erase Time (Parameter)	2	1	TDB	0.8	TDB	sec
		Block Erase Time (Main)	2	1.8	TDB	1.1	TDB	sec
	t_{WHRH5}, t_{EHRH5}	Program Suspend Latency		6	TDB	5	TDB	µs
	t_{WHRH6}, t_{EHRH6}	Erase Suspend Time		13	TDB	10	TDB	µs

NOTES:
1. Typical values measured at T_A = +25°C and nominal voltages. Subject to change based on device characterization.
2. Excludes system-level overhead.
3. These performance numbers are valid for all speed versions.
4. Sampled, but not 100% tested.
5. Reference the *AC Waveform for Write Operations* Figure 22.

9.0 ORDERING INFORMATION



VALID COMBINATIONS

		56-Lead SSOP	56-Lead TSOP	8 x 8 Easy BGA	56-Ball µBGA CSP(1)
Extended	**16M**	DT28F160F3T120	TE28F160F3T120	RC28F160F3T120	GT28F160F3T120
		DT28F160F3B120	TE28F160F3B120	RC28F160F3B120	GT28F160F3B120
		DT28F160F3T95	TE28F160F3T95	RC28F160F3T95	GT28F160F3T95
		DT28F160F3B95	TE28F160F3B95	RC28F160F3B95	GT28F160F3B95
Extended	**8M**	DT28F800F3T120	TE28F800F3T120	RC28F800F3T120	
		DT28F800F3B120	TE28F800F3B120	RC28F800F3B120	
		DT28F800F3T95	TE28F800F3T95	RC28F800F3T95	
		DT28F800F3B95	TE28F800F3B95	RC28F800F3B95	
Automtv.	**8M**	DE28F800B3T125			
		DE28F800B3B125			
		DE28F800B3T115			
		DE28F800B3B115			

NOTE:

1. The 56-Ball µBGA package top side mark reads F160F3. All product shipping boxes or trays provide the correct information regarding bus architecture.

10.0 ADDITIONAL INFORMATION[1,2]

Order Number	Document/Tool
210830	*Flash Memory Databook*
292213	*AP-655 3 Volt Fast Boot Block Design Guide*
297846	*Comprehensive User's Guide for µBGA* Packages*
Note 2	Fast Boot Block CPU Design Guide
Note 3	*µBGA* Package Mechanical and Shipping Media Specification* *Preliminary Mechanical Specification for Easy BGA Package*

NOTES:

1. Please call the Intel Literature Center at (800) 548-4725 to request Intel documentation. International customers should contact their local Intel or distribution sales office.
2. Visit Intel's World Wide Web home page at http://www.intel.com for technical documentation and tools.
3. See http://developer.intel.com/design/flash/packdata/ for packaging information.